

LM7480 3V~65V、バック・ツー・バック NFET 駆動、理想ダイオード・コントローラ

1 特長

- 拡張温度アプリケーション向けに認定済み
 - デバイス温度:
-55°C~+125°Cの動作時周囲温度範囲
- 3V~65V の入力範囲
- 最低 -65V までの逆入力保護
- 共通ドレインと共通ソースの構成で外付けのバック・ツー・バック N チャネル MOSFET を駆動
- アノードからカソードへ 10.5mV の順方向電圧降下レギュレーションを行う理想ダイオード動作 (LM74800)
- 低いスレッショルド (-4.5mV) と高速応答 (0.5μs) の逆電流検出
- 20mA のピーク・ゲート (DGATE) ターンオン電流
- 2.6A のピーク DGATE ターンオフ電流
- 調整可能な過電圧保護機能
- 低シャットダウン電流 (EN/UVLO = Low): 2.87μA
- 省スペースの 12 ピン WSON パッケージで供給

2 アプリケーション

- **アビオニクス入力の逆極性保護**
 - センサ
 - 画像処理
 - レーダー
- **冗長化電源用のアクティブ OR**

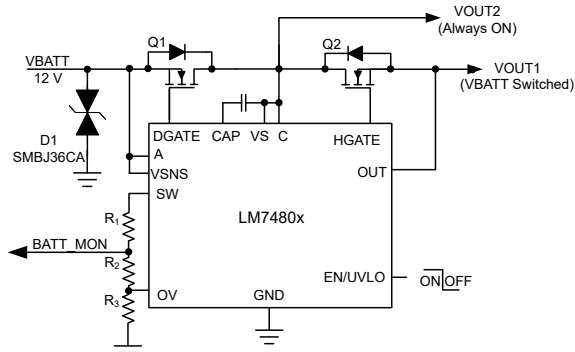
3 概要

LM7480 理想ダイオード・コントローラは外付けのバック・ツー・バック N チャネル MOSFET を駆動および制御して、電力パスの ON/OFF 制御と過電圧保護を備えた理想ダイオード整流器をエミュレートします。入力電源電圧範囲が 3V~65V と広いため、12V および 24V 入力電源システムを保護および制御できます。このデバイスは最低 -65V の負の電源電圧に耐え、この電圧から負荷を保護できます。内蔵の理想ダイオード・コントローラ (DGATE) は第 1 の MOSFET を駆動し、逆電流保護および出力電圧保持用のショットキー・ダイオードを置き換えます。電力パスの第 2 の MOSFET により、HGATE 制御を使用した負荷の切断 (ON/OFF 制御) と過電圧保護が可能です。このデバイスには可変の過電圧カットオフ保護機能があります。LM7480 には、LM74800 と LM74801 の 2 つのバリエーションがあります。LM74800 は、リニア・レギュレーションおよびコンパレータ方式を使用した逆電流ブロックを採用しています。一方、LM74801 はコンパレータに基づく方式をサポートしています。共通ドレイン構成のパワー MOSFET の場合、もう 1 つの理想ダイオードを使用した OR 接続設計のために中間点を利用できます。LM7480 は 65V の最大電圧定格を持っています。本デバイスと外付け MOSFET を共通ソース・トポロジに構成することで、24V バッテリ・システムの 200V 非抑制負荷ダンプのような大きな過電圧過渡からも負荷を保護できます。

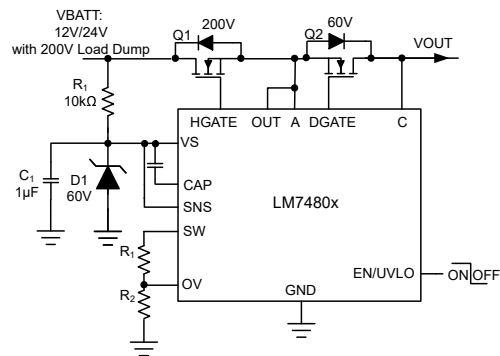
パッケージ情報

部品番号	パッケージ ⁽¹⁾	本体サイズ (公称)
LM74800	WSON (12)	3.00mm × 3.00mm
LM74801		

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



スイッチ出力を備えた理想ダイオード



200V 負荷ダンプ保護機能を備えた理想ダイオード



Table of Contents

1 特長	1	9.4 Device Functional Modes.....	16
2 アプリケーション	1	9.5 Application Examples.....	16
3 概要	1	10 Applications and Implementation	18
4 Revision History	2	10.1 Application Information.....	18
5 Device Comparison Table	3	10.2 Typical 12-V Reverse Battery Protection Application.....	18
6 Pin Configuration and Functions	3	10.3 200-V Unsuppressed Load Dump Protection Application.....	26
7 Specifications	4	10.4 Do's and Don'ts.....	29
7.1 Absolute Maximum Ratings.....	4	10.5 Power Supply Recommendations.....	29
7.2 ESD Ratings.....	4	10.6 Layout.....	31
7.3 Recommended Operating Conditions.....	4	11 Device and Documentation Support	33
7.4 Thermal Information.....	5	11.1 ドキュメントの更新通知を受け取る方法.....	33
7.5 Electrical Characteristics.....	5	11.2 サポート・リソース.....	33
7.6 Switching Characteristics.....	6	11.3 Trademarks.....	33
7.7 Typical Characteristics.....	8	11.4 静電気放電に関する注意事項.....	33
8 Parameter Measurement Information	10	11.5 用語集.....	33
9 Detailed Description	11	12 Mechanical, Packaging, and Orderable Information	33
9.1 Overview.....	11		
9.2 Functional Block Diagram.....	12		
9.3 Feature Description.....	13		

4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

DATE	REVISION	NOTES
December 2022	*	Initial Release

5 Device Comparison Table

	LM74800	LM74801
Reverse Current Blocking	$V_{(A-C)}$ linear regulation and comparator	$V_{(A-C)}$ comparator only

6 Pin Configuration and Functions

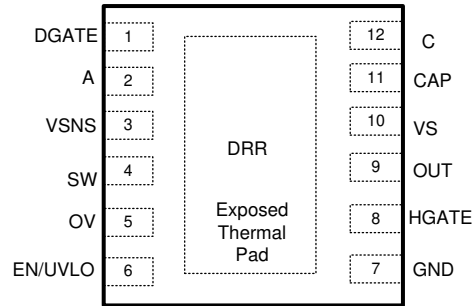


图 6-1. DRR Package, 12-Pin WSON (Top View)

表 6-1. Pin Functions

NAME	PIN		TYPE	DESCRIPTION
	LM7480	DRR-12 (WSON)		
DGATE	1	1	O	Diode Controller Gate Drive Output. Connect to the GATE of the external MOSFET.
A	2	2	I	Anode of the ideal diode. Connect to the source of the external MOSFET.
VSNS	3	3	I	Voltage sensing input.
SW	4	4	I	Voltage sensing disconnect switch terminal. VSNS and SW are internally connected through a switch. Use SW as the top connection of the battery sensing or OV resistor ladder network. When EN/UVLO is pulled low, the switch is OFF disconnecting the resistor ladder from the battery line thereby cutting off the leakage current. If the internal disconnect switch between VSNS and SW is not used then short them together and connect to VS pin.
OV	5	5	I	Adjustable overvoltage threshold input. Connect a resistor ladder across SW to OV terminal. When the voltage at OVP exceeds the overvoltage cut-off threshold then the HGATE is pulled low turning OFF the HSFET. HGATE turns ON when the sense voltage goes below the OVP falling threshold.
EN/UVLO	6	6	I	EN/UVLO Input. Connect to VS pin for always ON operation. Can be driven externally from a micro controller I/O. Pulling it low below $V_{(ENF)}$ makes the device enter into low Iq shutdown mode. For UVLO, connect an external resistor ladder to EN/UVLO to GND.
GND	7	7	G	Connect to the system ground plane.
HGATE	8	8	O	GATE driver output for the HSFET. Connect to the GATE of the external FET.
OUT	9	9	I	Connect to the output rail (external MOSFET source).
VS	10	10	I	Input power supply to the IC. Connect VS to middle point of the common drain back to back MOSFET configuration. Connect a 100-nF capacitor across VS and GND pins.
CAP	11	11	O	Charge pump output. Connect a 100-nF capacitor across CAP and VS pins.
C	12	12	I	Cathode of the ideal diode. Connect to the drain of the external MOSFET.
RTN	Thermal Pad	—	—	Leave exposed pad floating. Do Not connect to GND plane.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Input Pins	A to GND	-65	70	V
	VS to GND	-1	70	
	VSNS, SW, EN/UVLO, C, OV, OUT to GND, $V_{(A)} > 0$ V	-0.3	70	
	VSNS, SW, EN/UVLO, C, OV, OUT to GND, $V_{(A)} \leq 0$ V	$V_{(A)}$	$(70 + V_{(A)})$	
	RTN to GND	-65	0.3	mA
	I_{VSNS} , I_{SW}	-1	10	
	$I_{EN/UVLO}$, I_{OV} , $V_{(A)} > 0$ V	-1		
	$I_{EN/UVLO}$, I_{OV} , $V_{(A)} \leq 0$ V	Internally limited		
Output Pins	OUT to VS	-65	16.5	V
Output Pins	CAP to VS	-0.3	15	V
	CAP to A	-0.3	85	
	DGATE to A	-0.3	15	
	HGATE to OUT	-0.3	15	
Output to Input Pins	C to A	-5	85	
Operating junction temperature, T_j ⁽²⁾		-55	150	°C
Storage temperature, T_{stg}		-55	150	

- Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- High junction temperatures degrade operating lifetimes. Operating lifetime is de-rated for junction temperatures greater than 125°C.

7.2 ESD Ratings

			VALUE	UNIT	
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per JEDEC JS-001 ⁽¹⁾	±2000	V	
		Charged device model (CDM), V per JEDEC JS-002 ⁽²⁾	Corner pins (DGATE, OV, and C)		±750
			Other pins		±500

- JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- JEDEC document JEP155 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	NOM	MAX	UNIT
Input Pins	A to GND	-60		65	V
	VS to GND	0		65	V
	EN/UVLO to GND	0		65	V
External Capacitance	CAP to A, VS to GND, A to GND	0.1			µF
External MOSFET max VGS rating	DGATE to A and HGATE to OUT	15			V
T_j	Operating Junction temperature ⁽²⁾	-55		150	°C

- Recommended Operating Conditions are conditions under which the device is intended to be functional. For specifications and test conditions, see Electrical Characteristics.
- High junction temperatures degrade operating lifetimes. Operating lifetime is de-rated for junction temperatures greater than 125°C.

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		LM7480x	UNIT
		DRR (WSON)	
		12 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	60.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	48	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	31.5	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	1.2	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	31.4	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	7.1	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.5 Electrical Characteristics

$T_J = -55^{\circ}\text{C}$ to $+125^{\circ}\text{C}$; typical values at $T_J = 25^{\circ}\text{C}$, $V_{(A)} = V_{(OUT)} = V_{(VS)} = V_{(VSNS)} = 12\text{ V}$, $V_{(AC)} = 20\text{ mV}$, $C_{(VCAP)} = 0.1\text{ }\mu\text{F}$, $V_{(EN/UVLO)} = 2\text{ V}$, over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY VOLTAGE						
$V_{(VS)}$	Operating input voltage		3		65	V
$V_{(VS_PORR)}$	VS POR threshold, rising		2.4	2.6	2.85	V
$V_{(VS_PORF)}$	VS POR threshold, falling		1.9	2.1	2.3	V
$I_{(SHDN)}$	SHDN current, $I_{(GND)}$	$V_{(EN/UVLO)} = 0\text{ V}$		2.87	5	μA
$I_{(Q)}$	Total System Quiescent current, $I_{(GND)}$	$V_{(EN/UVLO)} = 2\text{ V}$		397		μA
		$V_{(A)} = V_{(VS)} = 24\text{ V}$, $V_{(EN/UVLO)} = 2\text{ V}$		413	530	μA
$I_{(REV)}$	$I_{(A)}$ leakage current during Reverse Polarity,	$0\text{ V} \leq V_{(A)} \leq -65\text{ V}$		10	112	μA
	$I_{(OUT)}$ leakage current during Reverse Polarity				1	μA
ENABLE AND UNDERVOLTAGE LOCKOUT (EN/UVLO) INPUT						
$V_{(UVLOR)}$	EN/UVLO threshold voltage, rising		1.195	1.231	1.267	V
$V_{(UVLOF)}$	EN/UVLO threshold voltage, falling		1.091	1.132	1.159	V
$V_{(ENF)}$	Enable threshold voltage for low Iq shutdown, falling		0.3	0.67	0.93	V
$V_{(EN_Hys)}$	Enable Hysteresis		37	72	95	mV
$I_{(EN/UVLO)}$		$0\text{ V} \leq V_{(EN/UVLO)} \leq 65\text{ V}$		55	200	nA
OVERVOLTAGE PROTECTION AND BATTERY SENSING (VSNS, SW, OV) INPUT						
$R_{(SW)}$	Battery sensing disconnect switch resistance	$3\text{ V} \leq V_{(SNS)} \leq 65\text{ V}$	10	19.5	46	Ω
$V_{(OVR)}$	Overvoltage threshold input, rising		1.195	1.231	1.267	V
$V_{(OVF)}$	Overvoltage threshold input, falling		1.091	1.13	1.159	V
$I_{(OV)}$	OV Input leakage current	$0\text{ V} \leq V_{(OV)} \leq 65\text{ V}$		53	200	nA
CHARGE PUMP (CAP)						
$I_{(CAP)}$	Charge Pump source current (Charge pump on)	$V_{(CAP)} - V_{(A)} = 7\text{ V}$, $6\text{ V} \leq V_{(S)} \leq 65\text{ V}$	1.3	2.7		mA
VCAP – VS	Charge Pump Turn ON voltage		11	12.2	13.2	V
	Charge Pump Turnoff voltage		11.9	13.2	14.1	V

7.5 Electrical Characteristics (continued)

$T_J = -55^\circ\text{C}$ to $+125^\circ\text{C}$; typical values at $T_J = 25^\circ\text{C}$, $V_{(A)} = V_{(OUT)} = V_{(VS)} = V_{(VSNS)} = 12\text{ V}$, $V_{(AC)} = 20\text{ mV}$, $C_{(VCAP)} = 0.1\ \mu\text{F}$, $V_{(EN/UVLO)} = 2\text{ V}$, over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(CAP\ UVLO)}$	Charge Pump UVLO voltage threshold, rising		5.4	6.6	7.9	V
	Charge Pump UVLO voltage threshold, falling		4.4	5.5	6.6	V
IDEAL DIODE (A, C, DGATE)						
$V_{(A_PORR)}$	$V_{(A)}$ POR threshold, rising		2.2	2.35	2.6	V
$V_{(A_PORF)}$	$V_{(A)}$ POR threshold, falling		2	2.2	2.4	V
$V_{(AC_REG)}$	Regulated Forward $V_{(A)}-V_{(C)}$ Threshold	For LM74800 Only	6.8	10	13.4	mV
$V_{(AC_REV)}$	$V_{(A)}-V_{(C)}$ Threshold for Fast Reverse Current Blocking		-6.5	-5.5	-1.3	mV
$V_{(AC_FWD)}$	$V_{(A)}-V_{(C)}$ Threshold for Reverse to Forward transition		150	177	220	mV
$V_{(DGATE)} - V_{(A)}$	Gate Drive Voltage	$3\text{ V} < V_{(S)} < 5\text{ V}$	7			V
		$5\text{ V} < V_{(S)} < 65\text{ V}$	10	11.5	13	V
$I_{(DGATE)}$	Peak Gate Source current	$V_{(A)} - V_{(C)} = 100\text{ mV}$, $V_{(DGATE)} - V_{(A)} = 1\text{ V}$		20		mA
	Peak Gate Sink current	$V_{(A)} - V_{(C)} = -12\text{ mV}$, $V_{(DGATE)} - V_{(A)} = 11\text{ V}$		2670		mA
	Regulation sink current	$V_{(A)} - V_{(C)} = 0\text{ V}$, $V_{(DGATE)} - V_{(A)} = 11\text{ V}$, LM74800 Only	7.2	12.3		μA
$I_{(C)}$	Cathode leakage Current	$V_{(A)} = -14\text{ V}$, $V_{(C)} = 12\text{ V}$, LM74801	0.1	2.84	15	μA
		$V_{(A)} = -14\text{ V}$, $V_{(C)} = 12\text{ V}$, LM74800	4	8.77	32	μA
HIGH SIDE CONTROLLER (HGATE, OUT, SNS, SW, OV)						
$V_{(HGATE)} - V_{(OUT)}$	Gate Drive Voltage	$3\text{ V} < V_{(S)} < 5\text{ V}$	7			V
		$5\text{ V} < V_{(S)} < 65\text{ V}$	10	11.1	14.5	V
$I_{(HGATE)}$	Source Current		39	55	75	μA
	Sink Current	$V_{(OV)} > V_{(OVR)}$	168	260		mA

7.6 Switching Characteristics

$T_J = -55^\circ\text{C}$ to $+125^\circ\text{C}$; typical values at $T_J = 25^\circ\text{C}$, $V_{(A)} = V_{(C)} = V_{(OUT)} = V_{(VS)} = 12\text{ V}$, $V_{(AC)} = 20\text{ mV}$, $C_{(VCAP)} = 0.1\ \mu\text{F}$, $V_{(EN/UVLO)} = 2\text{ V}$, over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{DGATE_OFF(dly)}$	DGATE Turnoff Delay during reverse voltage detection	$V_{(A)} - V_{(C)} = +30\text{ mV}$ to -100 mV to $V_{(DGATE-A)} < 1\text{ V}$, $C_{(DGATE-A)} = 10\text{ nF}$		0.5	0.875	μs
$t_{DGATE_ON(dly)}$	DGATE Turnon Delay during forward voltage detection	$V_{(A)} - V_{(C)} = -20\text{ mV}$ to $+700\text{ mV}$ to $V_{(DGATE-A)} > 5\text{ V}$, $C_{(DGATE-A)} = 10\text{ nF}$		2.8	3.8	μs
$t_{EN(dly)_DGATE}$	DGATE Turnon Delay during EN/UVLO	EN/UVLO \uparrow to $V_{(DGATE-A)} > 5\text{ V}$, $C_{(DGATE-A)} = 10\text{ nF}$	98	175	270	μs
$t_{EN_OFF(deg)_DGATE}$	DGATE Turnoff Deglitch during EN/UVLO	EN/UVLO \downarrow to DGATE \downarrow		8.1		μs
$t_{EN_OFF(deg)_HGATE}$	HGATE Turnoff Deglitch during EN/UVLO	EN/UVLO \downarrow to HGATE \downarrow	3	4.6	6	μs
$t_{OVP_OFF(deg)_HGATE}$	HGATE Turnoff Deglitch during OV	OV \uparrow to HGATE \downarrow , For LM74800 only		3.98	5.4	μs
		OV \uparrow to HGATE \downarrow , For LM74801 only		3.2	4.7	μs

7.6 Switching Characteristics (continued)

$T_J = -55^{\circ}\text{C}$ to $+125^{\circ}\text{C}$; typical values at $T_J = 25^{\circ}\text{C}$, $V_{(A)} = V_{(C)} = V_{(OUT)} = V_{(VS)} = 12\text{V}$, $V_{(AC)} = 20\text{ mV}$, $C_{(VCAP)} = 0.1\text{ }\mu\text{F}$, $V_{(EN/UVLO)} = 2\text{ V}$, over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{\text{OVP_ON(deg_HGATE)}}$	HGATE Turnon Deglitch during OV	OV ↓ to HGATE ↑		2.95		μs

7.7 Typical Characteristics

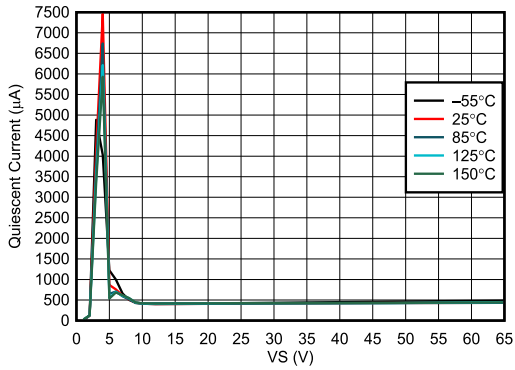


Figure 7-1. Operating Quiescent Current vs Supply Voltage

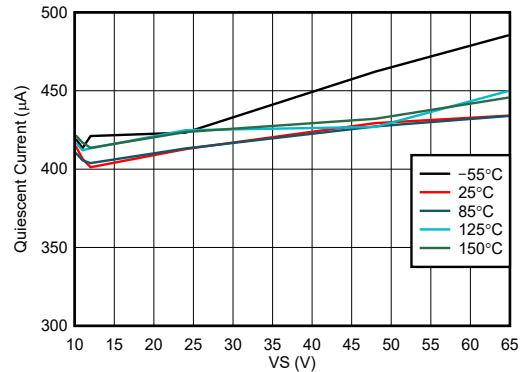


Figure 7-2. Operating Quiescent Current vs Supply Voltage (> 10 V)

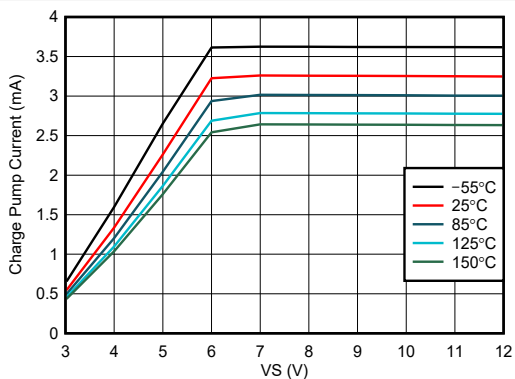


Figure 7-3. Charge Pump Current vs Supply Voltage at CAP = 6 V

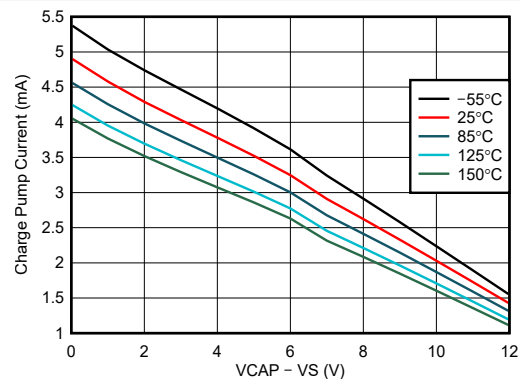


Figure 7-4. Charge Pump V-I Characteristics at VS ≥ 12 V

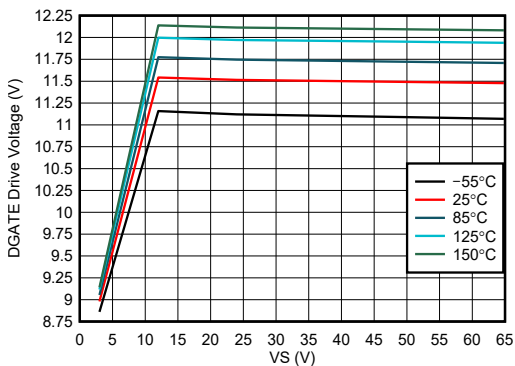


Figure 7-5. DGATE Drive Voltage vs Supply Voltage

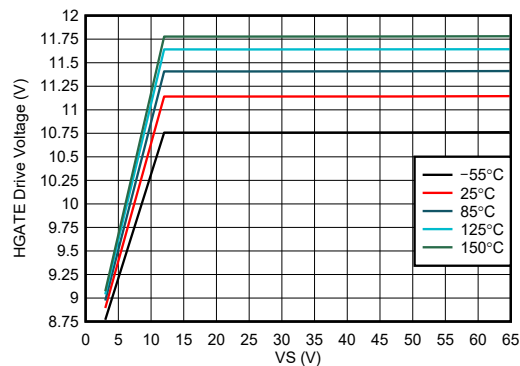


Figure 7-6. HGATE Drive Voltage vs Supply Voltage

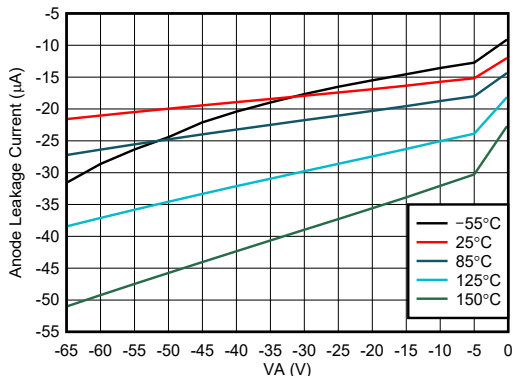


Figure 7-7. ANODE Leakage Current vs Reverse ANODE Voltage

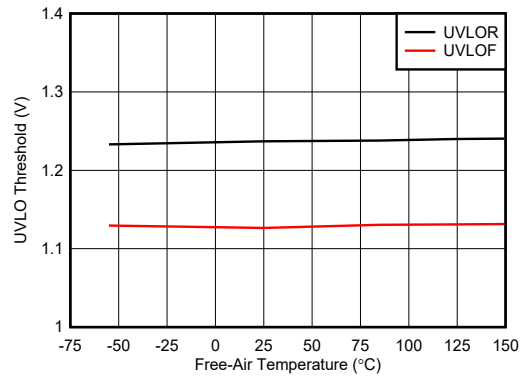
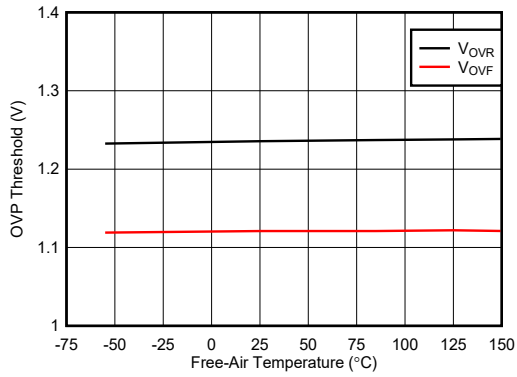
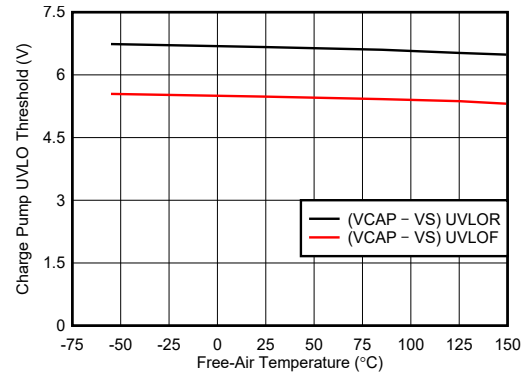


Figure 7-8. UVLO Thresholds vs Temperature

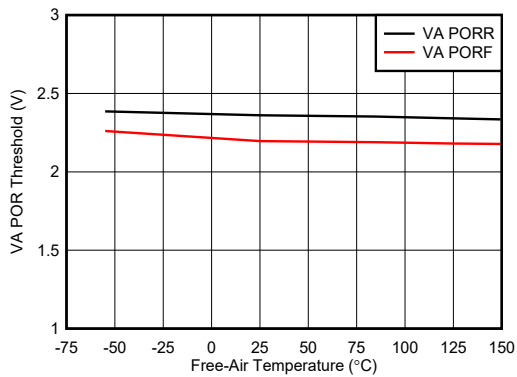
7.7 Typical Characteristics (continued)



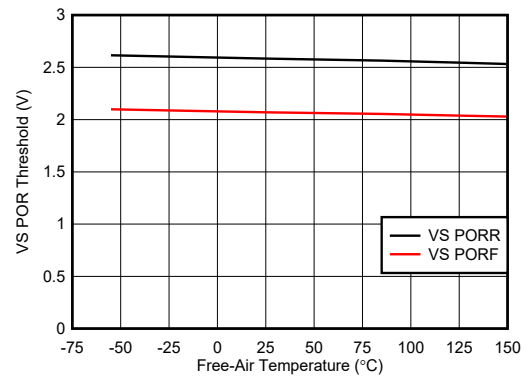
7-9. OVP Thresholds vs Temperature



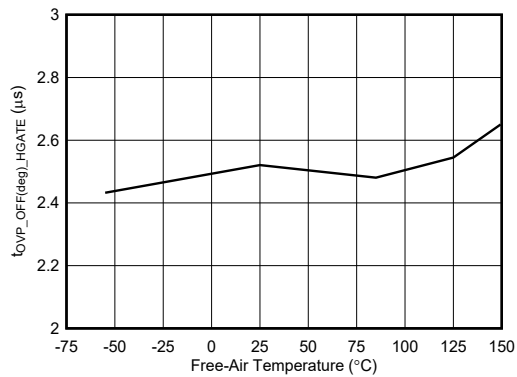
7-10. Charge Pump UVLO Threshold vs Temperature



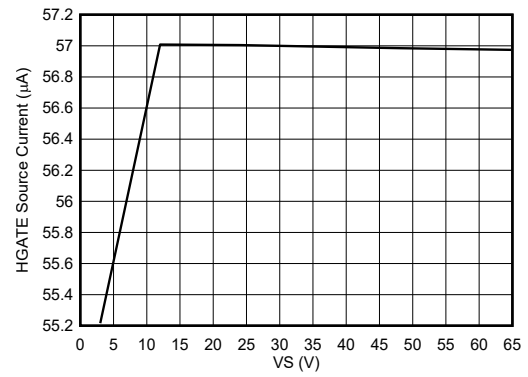
7-11. VA POR Threshold vs Temperature



7-12. VS POR Threshold vs Temperature

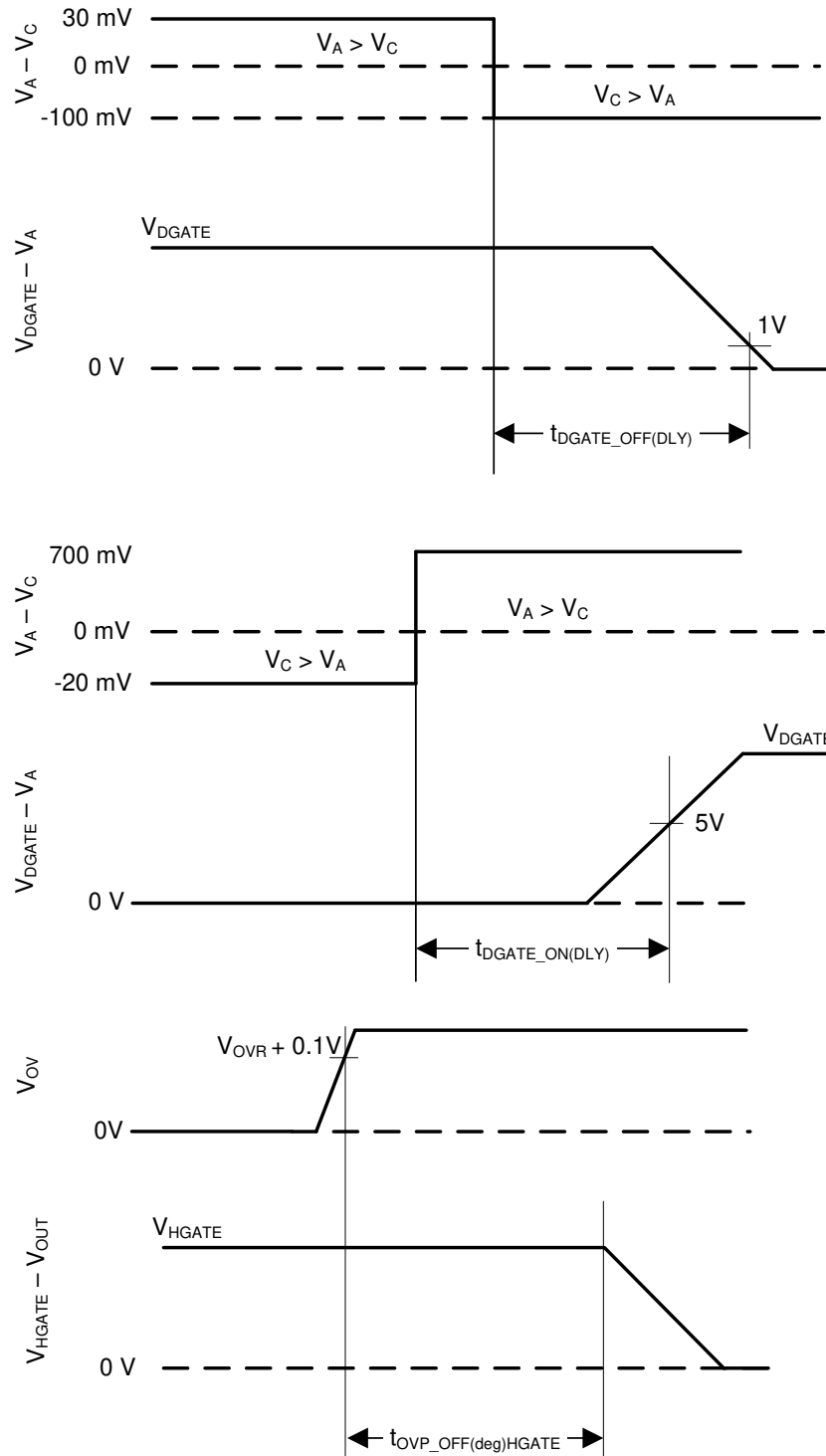


7-13. HGATE Turn OFF Delay During OV



7-14. HGATE Current (IHGATE) vs Supply Voltage

8 Parameter Measurement Information



8-1. Timing Waveforms

9 Detailed Description

9.1 Overview

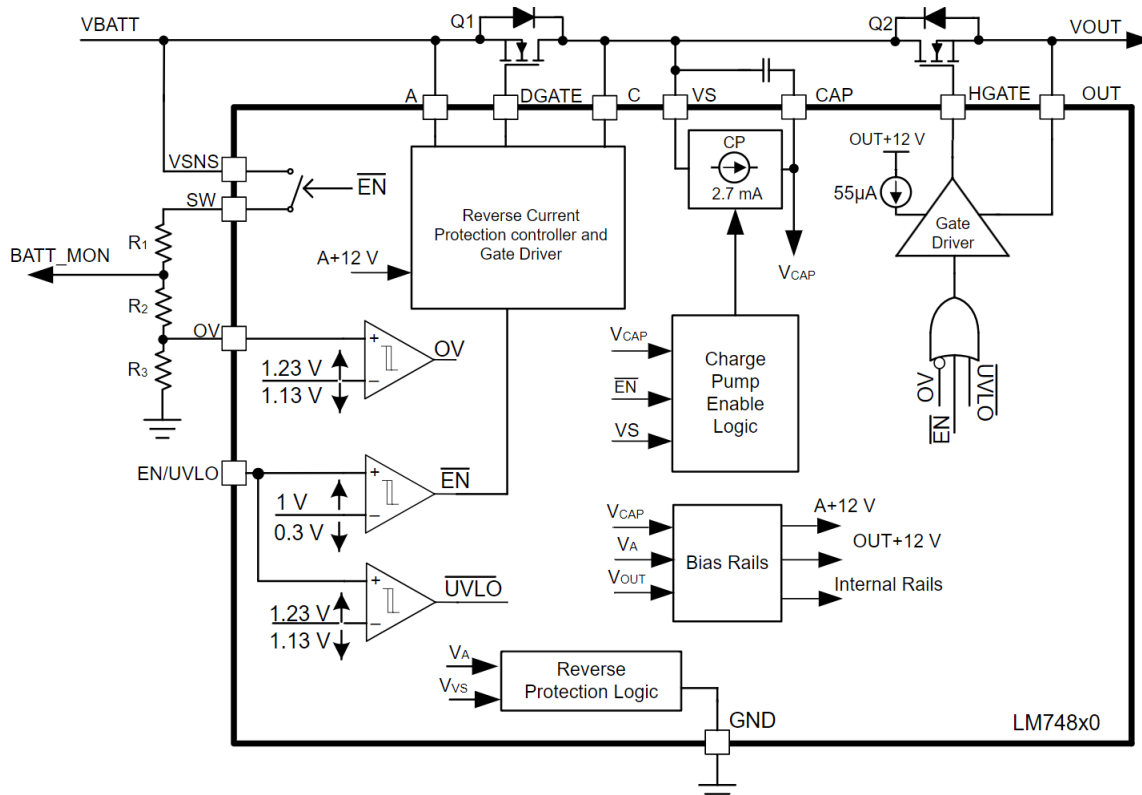
The LM7480 ideal diode controller drives and controls external back to back N-Channel MOSFETs to emulate an ideal diode rectifier with power path ON/OFF control, inrush current limiting and overvoltage protection. The wide input supply of 3 V to 65 V allows protection and control of 12-V and 24-V automotive battery powered ECUs. The device can withstand and protect the loads from negative supply voltages down to –65 V. An integrated ideal diode controller (DGATE) drives the first MOSFET to replace a Schottky diode for reverse input protection and output voltage holdup. A strong charge pump with 20-mA peak GATE source current driver stage and short turn ON and turn OFF delay times ensures fast transient response ensuring robust performance during automotive testing such as ISO16750 or LV124 where an ECU is subjected to AC superimpose input signals. With a second MOSFET in the power path the device allows load disconnect (ON/OFF control) and overvoltage protection using HGATE control. The device features an adjustable overvoltage cut-off protection feature using a programming resistor across SW and OVP terminal.

The LM7480 controller can drive the external MOSFETs in common drain and common source configurations. With common drain configuration of the power MOSFETs, the mid-point can be utilized for OR-ing designs using an another ideal diode. The LM7480 has a maximum voltage rating of 65 V. The loads can be protected from extended overvoltage transients like 200-V unsuppressed load dumps in 24-V battery systems by configuring the device with external MOSFETs in common source topology.

The LM74800 controls the DGATE of the MOSFET to regulate the forward voltage drop at 10.5 mV. The linear regulation scheme in these devices enables graceful control of the GATE voltage and turns off of the MOSFET during a reverse current event and ensures zero DC reverse current flow. The LM74801 features a comparator based scheme to turn ON/OFF the MOSFET GATE.

The device features enable control. With the enable pin low during the standby mode, both the external MOSFETs and controller is off and draws a very low 2.87 μ A of current. The high voltage rating of LM7480 helps to simplify the system designs for automotive ISO7637 protection. The LM74800 is also suitable for ORing applications.

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 Charge Pump

The charge pump supplies the voltage necessary to drive the external N-channel MOSFET. An external charge pump capacitor is placed between CAP and VS pins to provide energy to turn on the external MOSFET. In order for the charge pump to supply current to the external capacitor, the EN/UVLO pin voltage must be above the specified input high threshold, $V_{(ENR)}$. When enabled the charge pump sources a charging current of 2.7-mA typical. If EN/UVLO pin is pulled low, then the charge pump remains disabled. To ensure that the external MOSFET can be driven above its specified threshold voltage, the CAP to VS voltage must be above the undervoltage lockout threshold, typically 6.6 V, before the internal gate driver is enabled. Use 式 1 to calculate the initial gate driver enable delay.

$$T_{(DRV_EN)} = 175\mu\text{s} + C_{(CAP)} \times \frac{V_{(CAP_UVLOR)}}{2.7\text{mA}} \quad (1)$$

where

- $C_{(CAP)}$ is the charge pump capacitance connected across VS and CAP pins
- $V_{(CAP_UVLOR)} = 6.6\text{ V}$ (typical)

To remove any chatter on the gate drive approximately 1 V of hysteresis is added to the VCAP undervoltage lockout. The charge pump remains enabled until the CAP to VS voltage reaches 13.2 V, typically, at which point the charge pump is disabled decreasing the current draw on the VS pin. The charge pump remains disabled until the CAP to VS voltage is below to 12.2 V typically at which point the charge pump is enabled. The voltage between CAP and VS continue to charge and discharge between 12.2 V and 13.2 V as shown in 図 9-1. By enabling and disabling the charge pump, the operating quiescent current of the LM7480 is reduced. When the charge pump is disabled it sinks 15 μA .

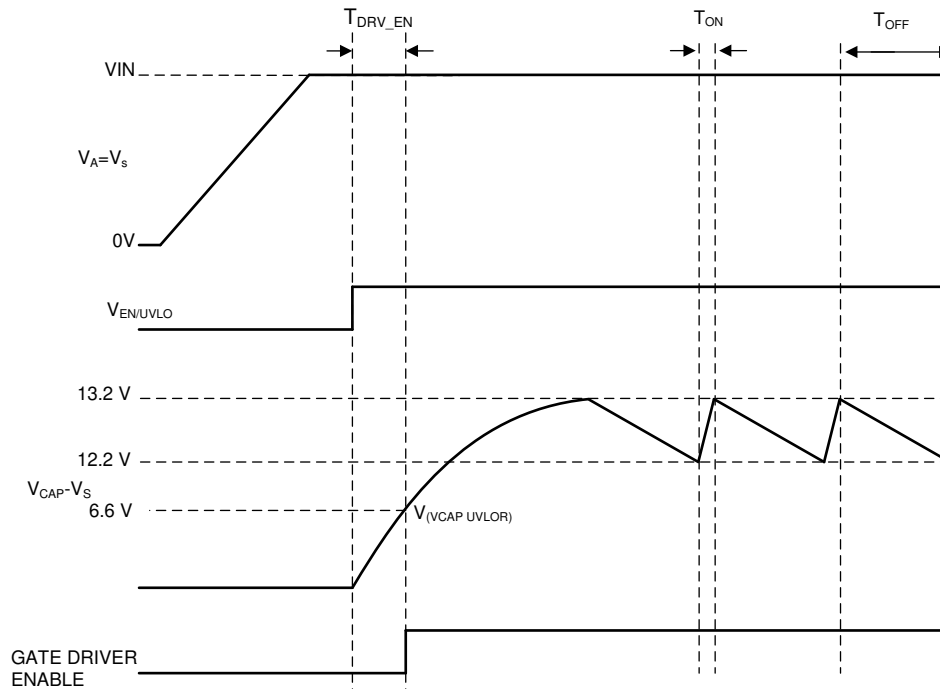


図 9-1. Charge Pump Operation

9.3.2 Dual Gate Control (DGATE, HGATE)

The LM7480x feature two separate gate control and driver outputs i.e DGATE and HGATE to drive back to back N-channel MOSFETs.

9.3.2.1 Reverse Battery Protection (A, C, DGATE)

A, C, DGATE comprises of Ideal Diode stage. Connect the Source of the external MOSFET to A, Drain to C and Gate to DGATE. The LM7480x has integrated reverse input protection down to -65 V .

Before the DGATE driver is enabled, following conditions must be achieved:

- The EN/UVLO pin voltage must be greater than the specified input high voltage.
- The CAP to VS voltage must be greater than the undervoltage lockout voltage.
- Voltage at A pin must be greater than VA POR Rising threshold.
- Voltage at Vs pin must be greater than Vs POR Rising threshold.

If the above conditions are not achieved, then the DGATE pin is internally connected to the A pin, assuring that the external MOSFET is disabled.

In LM74800 the voltage drop across the MOSFET is continuously monitored between the A and C pins, and the DGATE to A voltage is adjusted as needed to regulate the forward voltage drop at 10.5 mV (typ). This closed loop regulation scheme enables graceful turn off of the MOSFET during a reverse current event and ensures zero DC reverse current flow. This scheme ensures robust performance during slow input voltage ramp down tests. Along with the linear regulation amplifier scheme, the LM74800 also integrates a fast reverse voltage comparator. When the voltage drop across A and C reaches $V(\text{AC_REV})$ threshold then the DGATE goes low within $0.5\text{-}\mu\text{s}$ (typ). This fast reverse voltage comparator scheme ensures robust performance during fast input voltage ramp down tests such as input micro-shorts. The external MOSFET is turned ON back when the voltage across A and C hits $V(\text{AC_FWD})$ threshold within $2.8\text{ }\mu\text{s}$ (typ).

In LM74801, reverse current blocking is by fast reverse voltage comparator only. When the voltage drop across A and C reaches $V(\text{AC_REV})$ threshold then the DGATE goes low within $0.5\text{ }\mu\text{s}$ (typ). This fast reverse voltage comparator scheme ensures robust performance during fast input voltage ramp down tests such as input LM7480 micro-shorts. The external MOSFET is turned ON back when the voltage across A and C hits $V(\text{AC_FWD})$ threshold within $2.8\text{ }\mu\text{s}$ (typ).

For Ideal Diode only designs, connect LM7480x as shown in [Figure 9-2](#).

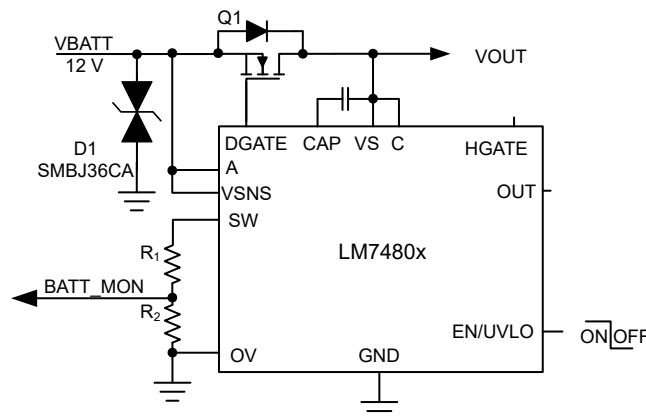


Figure 9-2. Configuring LM7480x-Q1 for Ideal Diode Only

9.3.2.2 Load Disconnect Switch Control (HGATE, OUT)

HGATE and OUT comprises of Load disconnect switch control stage. Connect the Source of the external MOSFET to OUT and Gate to HGATE.

Before the HGATE driver is enabled, following conditions must be achieved:

- The EN/UVLO pin voltage must be greater than the specified input high voltage.

- The CAP to VS voltage must be greater than the undervoltage lockout voltage.
- Voltage at Vs pin must be greater than Vs POR Rising threshold.

If the above conditions are not achieved, then the HGATE pin is internally connected to the OUT pin, assuring that the external MOSFET is disabled.

For Inrush Current limiting, connect C_{dVdT} capacitor and R_1 as shown in [Figure 9-3](#).

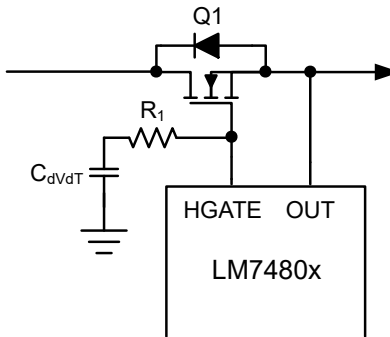


Figure 9-3. Inrush Current Limiting

The C_{dVdT} capacitor is required for slowing down the HGATE voltage ramp during power up for inrush current limiting. Use [Equation 2](#) to calculate C_{dVdT} capacitance value.

$$C_{dVdT} = \frac{I_{HGATE_DRV}}{I_{INRUSH}} \times C_{OUT} \quad (2)$$

where I_{HGATE_DRV} is 55 μ A (typ), I_{INRUSH} is the inrush current and C_{OUT} is the output load capacitance. An extra resistor, R_1 , in series with the C_{dVdT} capacitor improves the turn off time.

9.3.3 Overvoltage Protection and Battery Voltage Sensing (VSNS, SW, OV)

Connect a resistor ladder as shown in [Figure 9-4](#) for overvoltage threshold programming.

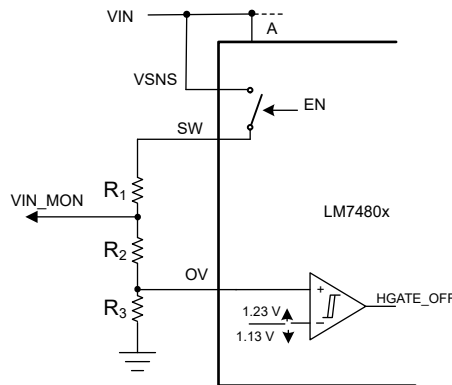


Figure 9-4. Programming Overvoltage Threshold and Battery Sensing

A disconnect switch is integrated between VSNS and SW pins. This switch is turned OFF when EN/UVLO pin is pulled low. This helps to reduce the leakage current through the resistor divider network during system shutdown state (IGN_OFF state).

LM7480-Q1 OV pin can also be used as a control input to turn off HGATE drive to achieve load disconnect functionality. When OV pin is driven high ($V_{OV} > V_{OVR}$), device pulls down HGATE to OUT thus turning off the load disconnect MOSFET. When OV pin is pulled low ($V_{OV} < V_{OVF}$) HGATE drive is again enabled to turn on the

load disconnect MOSFET. When OV pin is used as a control input to turn on/off load disconnect MOSFET, ensure device EN/UVLO pin is high ($V_{EN/UVLO} > V_{ENR}$) and SW/VSNS pin voltage is higher than OV pin voltage.

9.3.4 Low Iq Shutdown and Under Voltage Lockout (EN/UVLO)

The enable pin allows for the gate driver to be either enabled or disabled by an external signal. If the EN/UVLO pin voltage is greater than the rising threshold, the gate driver and charge pump operates as described in Charge Pump section. If EN/UVLO pin voltage is less than the input low threshold, $V_{(ENF)}$, the charge pump and both the gate drivers (DGATE and HGATE) are disabled placing the LM7480 in shutdown mode. If $V_{(ENF)} < V_{(EN/UVLO)} < V_{(UVLOF)}$ then only HGATE is disabled disconnecting the load from the supply, DGATE remains ON. The EN/UVLO pin can withstand a maximum voltage of 65 V. For always ON operation connect EN/UVLO pin to VS.

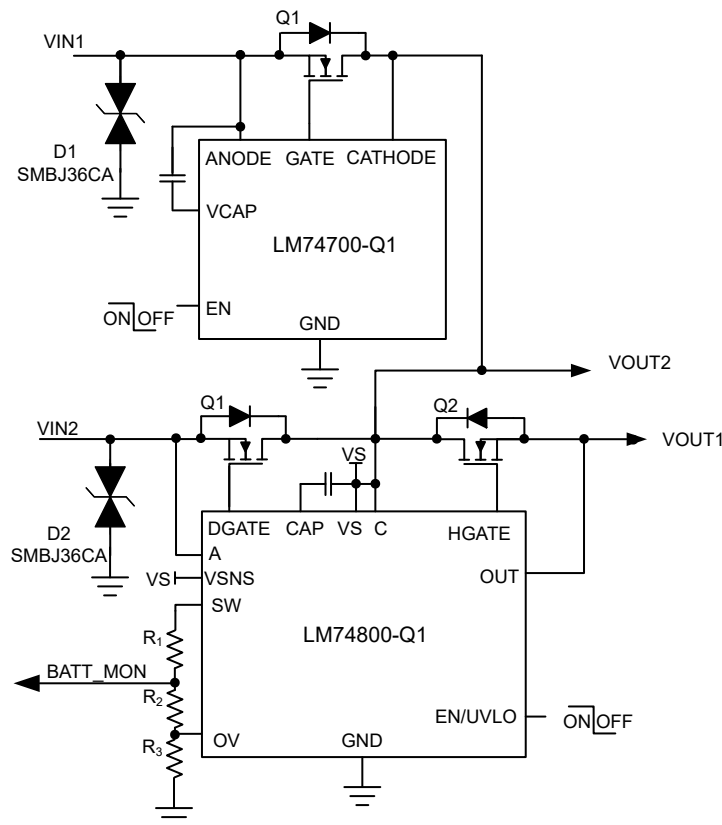
9.4 Device Functional Modes

Shutdown Mode

The LM7480 enters shutdown mode when the EN/UVLO pin voltage is below the specified input low threshold $V_{(ENF)}$. Both the gate drivers and the charge pump are disabled in shutdown mode. During shutdown mode the LM7480 enters low IQ operation with a total input quiescent consumption of 2.87 μA (typ). When the LM7480 is in shutdown mode, forward current flow to always ON loads connected to the common drain point of the back to back MOSFETs is not interrupted but is conducted through the MOSFET's body diode.

9.5 Application Examples

9.5.1 Redundant Supply OR-ing with Inrush Current Limiting, Overvoltage Protection and ON/OFF Control



9-5. Redundant Supply OR-ing with Overvoltage Protection and ON/OFF Control

Figure 9-5 shows the implementation of Dual OR-ing with Inrush Current Limiting, overvoltage Protection and power path ON/OFF control. The input side SMBJ36CA TVS across the ideal diodes is required for ISO7637 Pulse 1 transient suppression to limit the input voltage within the device max voltage rating of -65V .

R1 and R2 are the programming resistors for over voltage protection (OVP) threshold. When the voltage at OV pin exceeds OV cut-off reference threshold then the HGATE driver turns OFF the FET Q3, disconnecting the power path and protecting the downstream load. HGATE goes high once the OVP pin voltage goes below the OVP falling hysteresis threshold. Use $0.1\text{-}\mu\text{F}$ to $1\text{-}\mu\text{F}$ capacitor across VS to CAP pins of the LM7480. This is the charge pump capacitor and acts as the supply for both the DGATE and HGATE driver stages. The DGATE driver of the LM7480 is equipped with 20-mA peak source current and 2.6-A peak sink current capability resulting in fast and efficient transient responses during the ISO16750 or LV124 short interruptions as well as AC superimpose testing.

Pull EN low during the sleep/standby mode. With EN low, both the DGATE and HGATE drivers are pulled low turning OFF both the power FETs. VOUT1 gets disconnected from the input supply rail reducing the system I_Q . VOUT2 is gets power through the body diode of the MOSFET Q2 and this supply can be utilized for always ON loads. The LM7480 draws a $2.87\text{-}\mu\text{A}$ (typ) current during this mode.

9.5.2 Ideal Diode With Unsuppressed Load Dump Protection

An extended overvoltage protection support above 65 V can be achieved by configuring the device with external back to back MOSFETs in common source topology as shown in Figure 9-6. Place a resistor R1 and a zener clamp across VS pin to GND to limit the voltage below 65 V . The load gets protected from overvoltages transients like unsuppressed load dumps with the help of overvoltage protection feature. Use R2 and R3 for setting the overvoltage protection threshold. When voltage at OV pin exceeds the set OV threshold then the HGATE turns OFF. This results in power path disconnection between input and output.

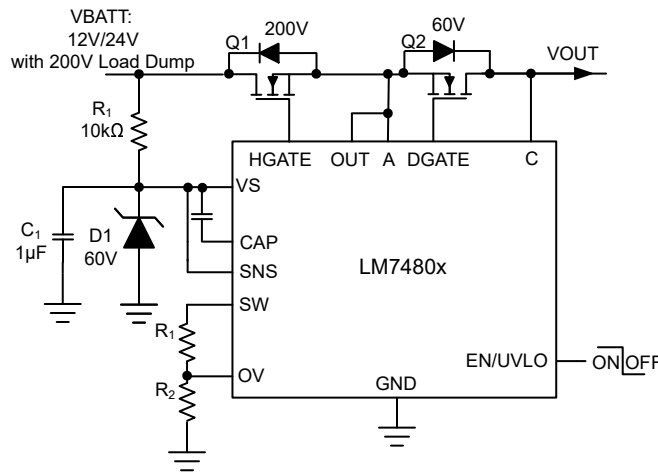


Figure 9-6. Ideal Diode With 200-V Unsuppressed Load Dump Protection

10 Applications and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

10.1 Application Information

LM7480 controls two N-channel power MOSFETs with DGATE used to control diode MOSFET to emulate an ideal diode and HGATE controlling second MOSFET for power path cut-off when disabled or during an overvoltage protection. HGATE controlled MOSFET can be used to clamp the output during overvoltage or load dump conditions. LM7480 can be placed into low quiescent current mode using EN/UVLO, where both DGATE and HGATE are turned OFF.

The device has a separate supply input pin (Vs). The charge pump is derived from this supply input. With the separate supply input provision and separate GATE control architecture, the LM7480 device offers flexibility in system design architectures and enables circuit design with various power path control topologies like common drain, common source, ORing and Power MUXing. With these various topologies, the system designers can design the front-end power system to meet various system design requirements. For more information, see the [Six System Architectures With Robust Reverse Battery Protection Using an Ideal Diode Controller](#) Application Report.

10.2 Typical 12-V Reverse Battery Protection Application

A typical application circuit of LM74800 configured in **common-drain topology** to provide reverse battery protection with overvoltage protection is shown in [Figure 10-1](#).

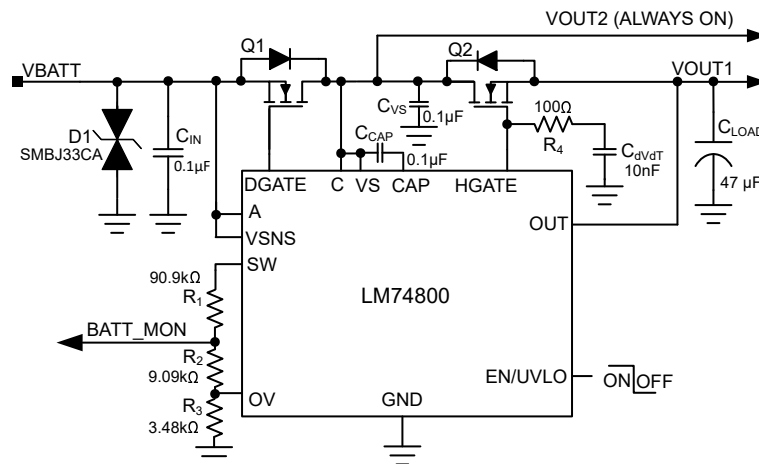


Figure 10-1. Typical Application Circuit: 12-V Reverse Battery Protection and Overvoltage Protection

10.2.1 Design Requirements for 12-V Battery Protection

The system design requirements are listed in [表 10-1](#).

表 10-1. Design Parameters for 12-V Reverse Battery Protection and Overvoltage Protection

DESIGN PARAMETER	EXAMPLE VALUE
Operating Input Voltage Range	12-V battery, 12-V nominal with 3.2-V cold crank and 35-V load dump
Output Power	50 W
Output Current Range	4-A nominal, 5-A maximum
Input Capacitance	0.1- μ F minimum
Output Capacitance	0.1- μ F minimum (optional hold-up capacitor of 47 μ F)
Overvoltage Cut-off	37 V, output cut-off > 37 V
Battery Monitor Ratio	8:1

10.2.2 Automotive Reverse Battery Protection

The LM7480 feature two separate gate control and driver outputs i.e DGATE and HGATE to drive back to back N-channel MOSFETs. This enables LM7480 to provide comprehensive immunity with robust system protection during various automotive transient tests as per ISO 7637-2 and ISO 16750-2 standard as well as other automotive OEM standards. For more information, see the [Automotive EMC-compliant reverse-battery protection with ideal-diode controllers](#) article.

LM7480 gate drive output DGATE controls MOSFET Q1 to provide reverse battery protection and true reverse current blocking functionality. HGATE controls MOSFET Q2 to turn off the power path during input overvoltage condition. Resistor network R1, R2 and R3 connected to OV and SW can be configured for overvoltage protection and also for battery monitoring under normal operating conditions as well as reverse battery conditions. Bi-directional TVS D1 clamps the automotive transient input voltages on the 12-V battery, both positive and negative transients, to voltage levels safe for MOSFET Q1 and LM7480.

Fast reverse current blocking response and quick reverse recovery enables LM7480 to turn ON/OFF MOSFET Q1 during AC super imposed input and provide active rectification of the AC input superimposed on DC battery voltage. Fast reverse current blocking response of LM7480 helps to turn off MOSFET Q1 during negative transients inputs and input micro short interruption conditions where input can fall to 0-V for short duration.

10.2.3 Detailed Design Procedure

10.2.3.1 Design Considerations

表 10-1 summarizes the design parameters that must be known for designing an automotive reverse battery protection circuit with overvoltage cut-off. During power up, inrush current through MOSFET Q2 needs to be limited so that the MOSFET operates well within its SOA. Maximum load current, maximum ambient temperature and thermal properties of the PCB determine the $R_{DS(ON)}$ of the MOSFET Q2 and maximum operating voltage determines the voltage rating of the MOSFET Q2. Selection of MOSFET Q2 is determined mainly by the maximum operating load current, maximum ambient temperature, maximum frequency of AC super imposed voltage ripple and ISO 7637-2 pulse 1 requirements. overvoltage threshold is decided based on the rating of downstream DC/DC converter or other components after the reverse battery protection circuit. A single bi-directional TVS or two back-back uni-directional TVS are required to clamp input transients to a safe operating level for the MOSFETs Q1, Q2 and LM7480.

10.2.3.2 Charge Pump Capacitance VCAP

Minimum required capacitance for charge pump VCAP is based on input capacitance of the MOSFET Q1, $C_{ISS(MOSFET_Q1)}$ and input capacitance of Q2 $C_{ISS(MOSFET)}$.

Charge Pump VCAP: Minimum 0.1 μF is required; recommended value of VCAP (μF) $\geq 10 \times (C_{ISS(MOSFET_Q1)} + C_{ISS(MOSFET_Q2)})$ (μF)

10.2.3.3 Input and Output Capacitance

A minimum input capacitance C_{IN} of 0.1 μF and output capacitance C_{OUT} of 0.1 μF is recommended.

10.2.3.4 Hold-Up Capacitance

Usually bulk capacitors are placed on the output due to various reasons such as uninterrupted operation during power interruption or micro-short at the input, hold-up requirements for doing a memory dump before turning of the module and filtering requirements as well. This design considers minimum bulk capacitors requirements for meeting functional status "A" during LV124 E10 test case 2 100- μs input interruption. To achieve functional pass status A, acceptable voltage droop in the output of LM7480 is based on the UVLO settings of downstream DC-DC converters. For this design, 2.5-V drop in output voltage for 100 μs is considered and the minimum hold-up capacitance required is calculated by

$$C_{HOLD_UP_MIN} = \frac{I_{LOAD_MAX}}{dV_{OUT}} \times 100 \mu\text{s} \quad (3)$$

Minimum hold-up capacitance required for 2.5-V drop in 100 μs is 200 μF . Note that the typical application circuit shows the hold-up capacitor as optional because not all designs require hold-up capacitance.

10.2.3.5 Overvoltage Protection and Battery Monitor

Resistors R_1 , R_2 and R_3 connected in series are used to program the overvoltage threshold and battery monitor ratio. The resistor values required for setting the overvoltage threshold V_{OV} to 37.0 V and battery monitor ratio $V_{BATT_MON} : V_{BATT}$ to 1:8 are calculated by solving Equation 3 and Equation 4.

$$V_{OVR} = \frac{R_3}{R_1 + R_2 + R_3} \times V_{OV} \quad (4)$$

$$V_{BAT_MON} = \frac{R_2 + R_3}{R_1 + R_2 + R_3} \times V_{BATT} \quad (5)$$

For minimizing the input current drawn from the battery through resistors R_1 , R_2 and R_3 , it recommended to use higher value of resistance. Using high value resistors will add error in the calculations because the current

through the resistors at higher value will become comparable to the leakage current into the OV pin. Maximum leakage current into the OV pin is 1 μ A and choosing $(R_1 + R_2 + R_3) < 120$ k Ω ensures current through resistors is 100 times greater than leakage through OV pin.

Based on the device electrical characteristics, V_{OVR} is 1.23 V and battery monitor ratio (V_{BATT_MON} / V_{BATT}) is designed for a ratio of 1/8. To limit $(R_1 + R_2 + R_3) < 120$ k Ω , select $(R_1 + R_2) = 100$ k Ω . Solving Equation 3 gives $R_3 = 3.45$ k Ω . Solving Equation 4 for R2 using $(R_1 + R_2) = 100$ k Ω and $R_3 = 3.45$ k Ω , gives $R_2 = 9.48$ k Ω and $R_1 = 90.52$ k Ω .

Standard 1% resistor values closest to the calculated resistor values are $R_1 = 90.9$ k Ω , $R_2 = 9.09$ k Ω and $R_3 = 3.48$ k Ω .

10.2.4 MOSFET Selection: Blocking MOSFET Q1

For selecting the blocking MOSFET Q1, important electrical parameters are the maximum continuous drain current I_D , the maximum drain-to-source voltage $V_{DS(MAX)}$, the maximum drain-to-source voltage $V_{GS(MAX)}$, the maximum source current through body diode and the drain-to-source ON resistance $R_{DS(ON)}$.

The maximum continuous drain current, I_D , rating must exceed the maximum continuous load current.

The maximum drain-to-source voltage, $V_{DS(MAX)}$, must be high enough to withstand the highest differential voltage seen in the application. This would include all the automotive transient events and any anticipated fault conditions. It is recommended to use MOSFETs with V_{DS} voltage rating of 60 V along with a single bidirectional TVS or a V_{DS} rating 40-V maximum rating along with two unidirectional TVS connected back-back at the input.

The maximum V_{GS} LM7480 can drive is 14 V, so a MOSFET with 15-V minimum V_{GS} rating should be selected. If a MOSFET with < 15 -V V_{GS} rating is selected, a zener diode can be used to clamp V_{GS} to safe level, but this would result in increased I_Q current.

To reduce the MOSFET conduction losses, lowest possible $R_{DS(ON)}$ is preferred, but selecting a MOSFET based on low $R_{DS(ON)}$ may not be beneficial always. Higher $R_{DS(ON)}$ will provide increased voltage information to LM7480's reverse comparator at a lower reverse current. Reverse current detection is better with increased $R_{DS(ON)}$. Choosing a MOSFET with < 50 -mV forward voltage drop at maximum current is a good starting point.

For active rectification of AC super imposed ripple on the battery supply voltage, gate-source charge Q_{GS} of Q1 must be selected to meet the required AC ripple frequency. Maximum gate-source charge Q_{GS} (at 4.5-V V_{GS}) for active rectification every cycle is

$$Q_{GS_MAX} = \frac{1.3\text{mA}}{F_{AC_RIPPLE}} \quad (6)$$

Where 1.3 mA is minimum charge pump current at 7-V $V_{DGATE-V_A}$, F_{AC_RIPPLE} is frequency of the AC ripple superimposed on the battery and Q_{GS_MAX} is the Q_{GS} value specified in manufacturer datasheet at 6-V V_{GS} . For active rectification at $F_{AC_RIPPLE} = 30$ KHZ, $Q_{GS_MAX} = 43$ nC.

Based on the design requirements, BUK7Y4R8-60E MOSFET is selected and its ratings are:

- 60-V $V_{DS(MAX)}$ and ± 20 -V $V_{GS(MAX)}$
- $R_{DS(ON)}$ 5.0-m Ω typical at 5-V V_{GS} and 2.9-m Ω rated at 10-V V_{GS}
- MOSFET Q_{GS} 17.4 nC

Thermal resistance of the MOSFET should be considered against the expected maximum power dissipation in the MOSFET to ensure that the junction temperature (T_J) is well controlled.

10.2.5 MOSFET Selection: Hot-Swap MOSFET Q2

The V_{DS} rating of the MOSFET Q2 should be sufficient to handle the maximum system voltage along with the input transient voltage. For this 12-V design, transient overvoltage events are during suppressed load dump 35 V 400 ms and ISO 7637-2 pulse 2 A 50 V for 50 μ s. Further, ISO 7637-2 Pulse 3B is a very fast repetitive pulse of 100 V 100 ns that is usually absorbed by the input and output ceramic capacitors and the maximum voltage on the 12-V battery can be limited to < 40 V the minimum recommended input capacitance of 0.1 μ F. The 50-V

SO 7637-2 Pulse 2 A can also be absorbed by input and output capacitors and its amplitude could be reduced to 40-V peak by placing sufficient amount of capacitance at input and output. However for this 12-V design, maximum system voltage is 50 V and a 60-V V_{DS} rated MOSFET is selected.

The VGS rating of the MOSFET Q2 should be higher than that maximum HGATE-OUT voltage 15 V.

Inrush current through the MOSFET during input hot-plug into the 12-V battery is determined by output capacitance. External capacitor on HGATE, C_{DVRT} is used to limit the inrush current during input hot-plug or startup. The value of inrush current determined by 式 2 need to be selected to ensure that the MOSFET Q2 is operating well within its safe operating area (SOA). To limit inrush current to 250 mA, value of C_{DVRT} is 10.43 nF, closest standard value of 10.0 nF is chosen.

Duration of inrush current is calculated by

$$dT_{INRUSH} = \frac{12}{I_{INRUSH}} \times C_{OUT} \quad (7)$$

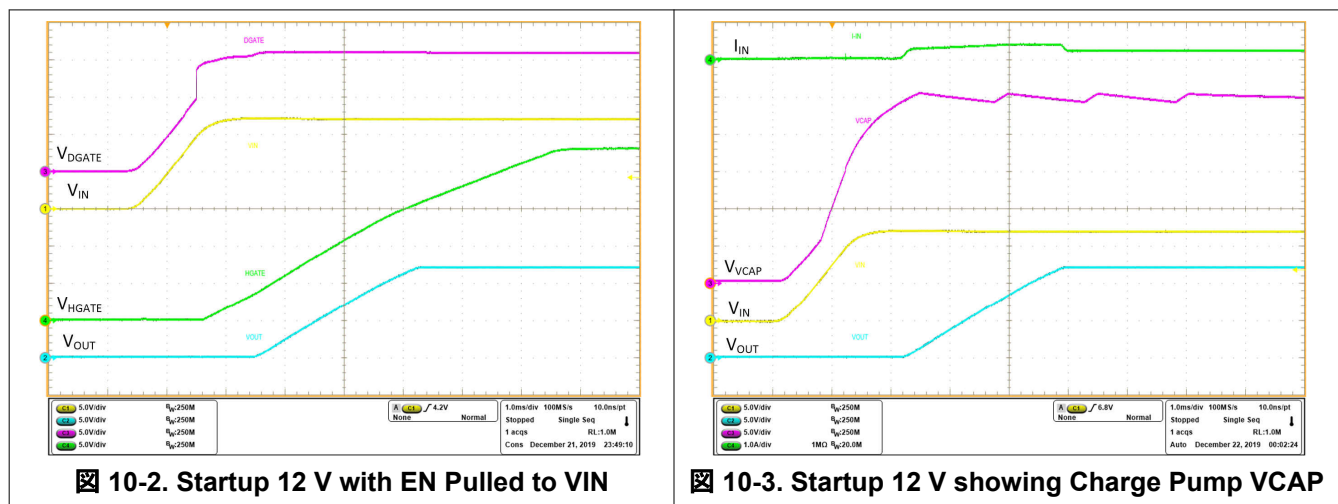
Calculated inrush current duration is 2.36 ms with 250-mA inrush current.

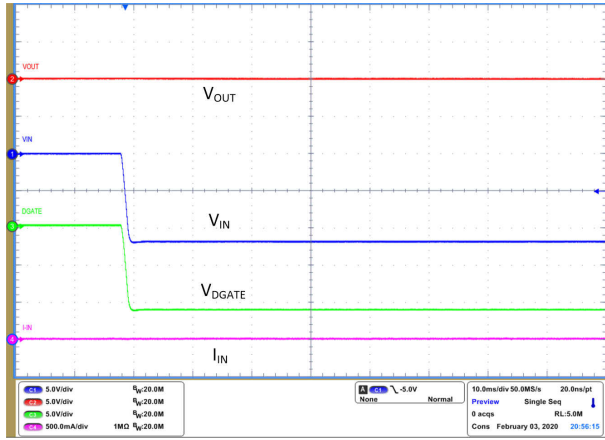
MOSFET BUK7Y4R8-60E having 60-V V_{DS} and ± 20 -V V_{GS} rating is selected for Q2. Power dissipation during inrush is well within the MOSFET's safe operating area (SOA).

10.2.6 TVS Selection

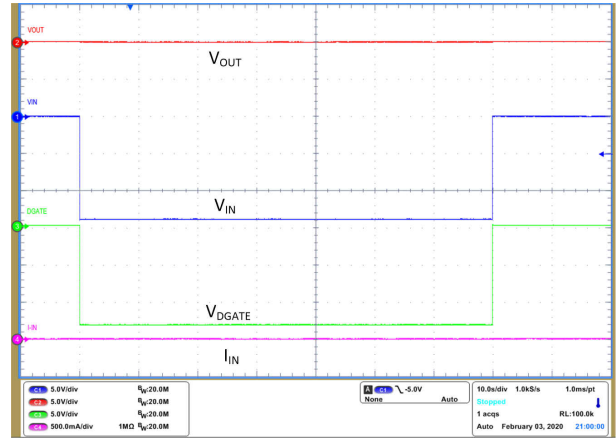
A 600-W SMBJ TVS such as SMBJ33CA is recommended for input transient clamping and protection. For detailed explanation on TVS selection for 12-V battery systems, refer to [TVS Selection for 12-V Battery Systems](#).

10.2.7 Application Curves

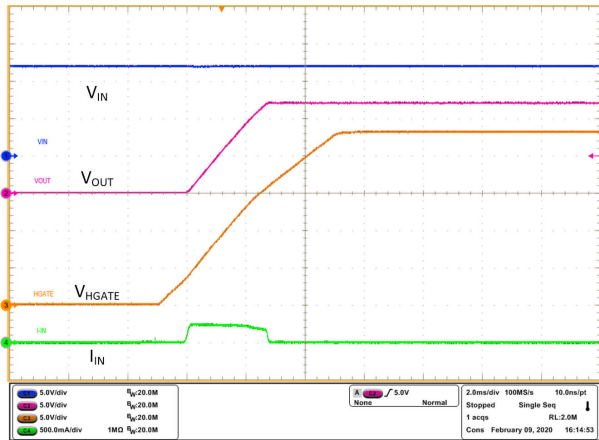




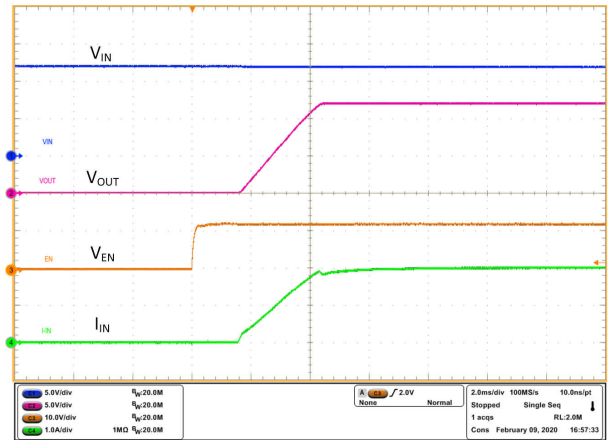
10-4. Reverse Input Voltage –14 V



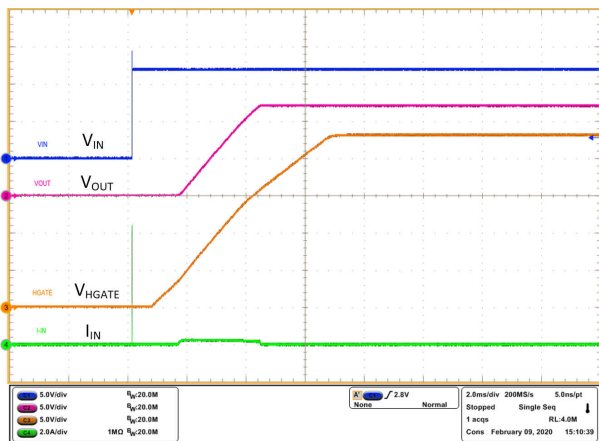
10-5. Reverse Input Voltage –14 V for 60 s



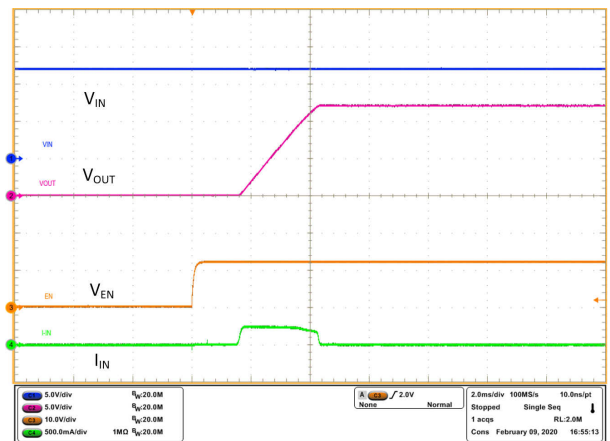
10-6. Inrush Current with no Load at Output



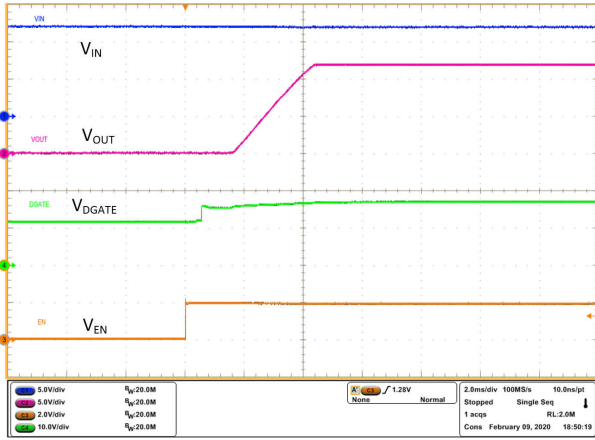
10-7. Inrush Current with 60-Ω Load



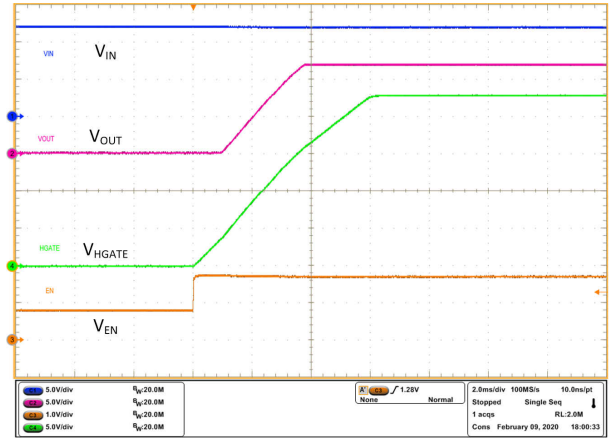
10-8. Hot-Plug into 12 V



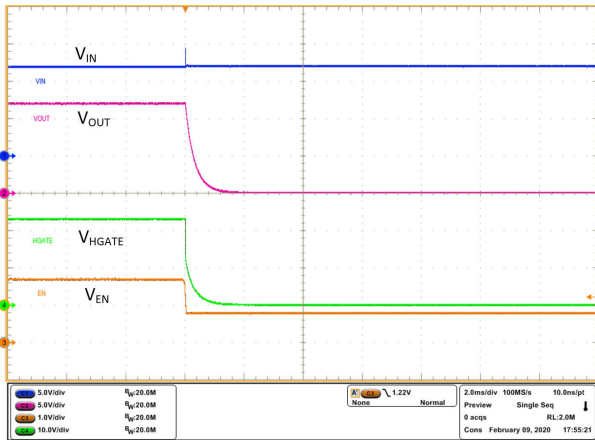
10-9. Output Turn ON with Enable



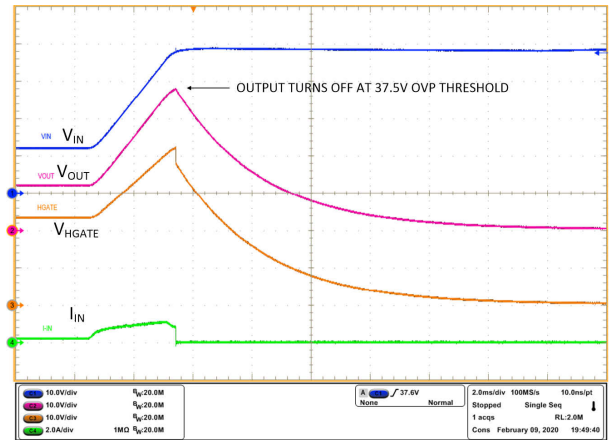
10-10. DGATE Turn ON with Enable



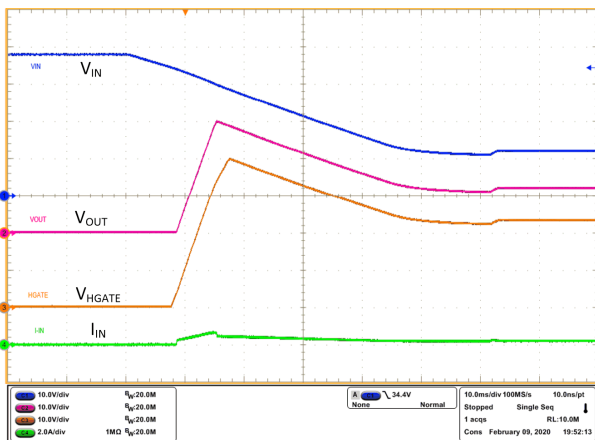
10-11. Turn ON with VCAP ON - EN rising from 0.8 V



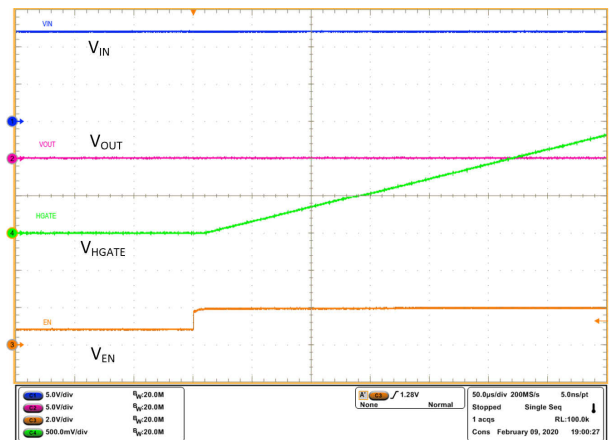
10-12. Turn OFF with Enable Control



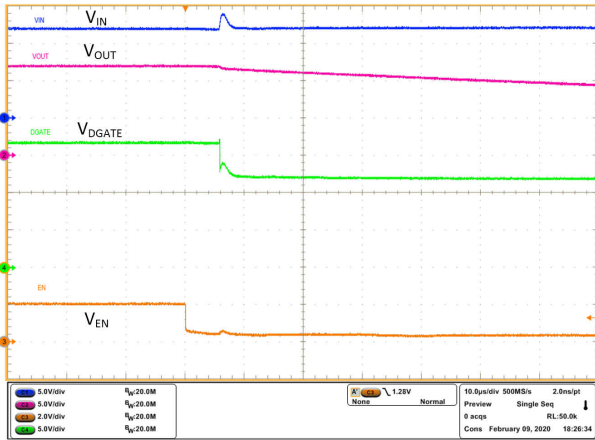
10-13. Overvoltage Protection



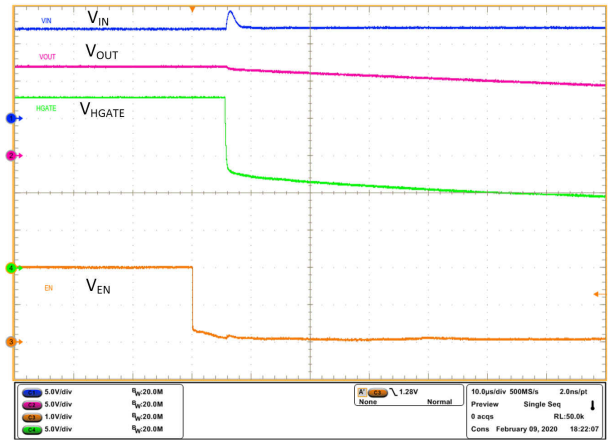
10-14. Overvoltage Recovery



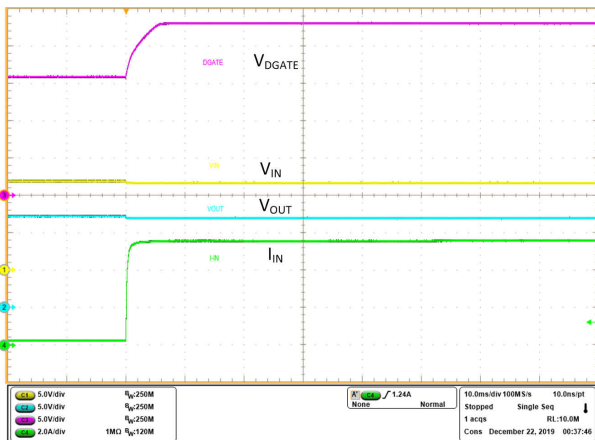
10-15. Turn ON delay - HGATE



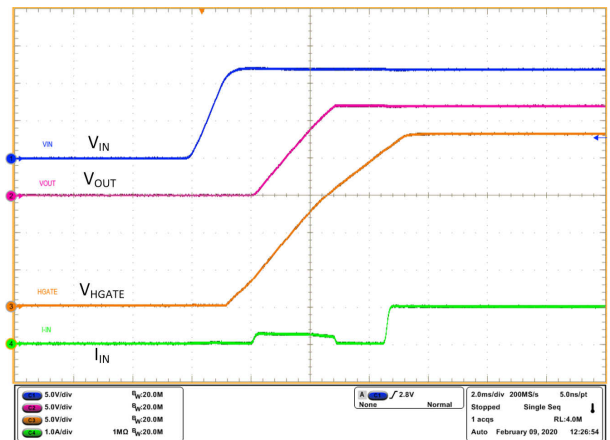
10-16. Turn OFF Delay - DGATE



10-17. Turn OFF Delay - HGATE



10-18. Load Transient 100 mA to 5 A



10-19. Startup 1-A Load 1 ms After Output Powers Up

10.3.2.1 Boost Converter Components (C2, C3, L1)

Place a minimum of 1- μ F capacitor across drain of the FET to GND (C2) and across CAP pin of LM7472x-Q1 to drain of the FET (C3). Use a 100- μ H inductor (L1) with saturation current rating > 175 mA (for example, XPL2010-104ML from coil craft).

10.3.2.2 Input and Output Capacitance

A minimum input capacitance C_{IN} of 0.1 μ F and output capacitance C_{OUT} of 0.1 μ F is recommended.

10.3.2.3 V_S Capacitance, Resistor, and Zener Clamp

Minimum of 1- μ F C_{VS} capacitance is required. During 200-V load dump, resistor R_1 and Zener diode D_1 are used to protect V_S pin from exceeding the maximum ratings by clamping V_{VS} to 60 V. Choosing $R_1 = 10$ k Ω , the peak power dissipated in Zener diode $D1 = 60$ V \times (200 V – 60 V) / 10 k $\Omega = 0.840$ W of peak power dissipation. SMA package diode such as BZG03B62-M can handle 840-mW peak power dissipation. Peak power dissipated in $R1 = (200$ V – 60 V)² / 10 k $\Omega = 1.96$ W. One 10-k Ω resistor in 1210 package with 0.5-W DC power rating and 200-V rating can withstand 200-V load dump for 350 ms.

10.3.2.4 Overvoltage Protection and Output Clamp

Resistors R_2 and R_3 connected in series is used to program the overvoltage threshold. Connecting R_2 to VBATT provides overvoltage cut-off and switching the connection to VOUT provides overvoltage clamp. The resistor values required for setting the overvoltage threshold V_{OV} to 37.0 V is calculated by solving [Equation 7](#).

$$V_{OVR} = \frac{R_3}{R_2 + R_3} \times V_{OV} \quad (8)$$

For minimizing the input current drawn from the battery through resistors R_2 and R_3 , it recommended to use higher value of resistance. Using high value resistors will add error in the calculations because the current through the resistors at higher value will become comparable to the leakage current into the OV pin. Maximum leakage current into the OV pin is 1 μ A and choosing $(R_2 + R_3) < 120$ k Ω ensures current through resistors is 100 times greater than leakage through OV pin.

Based on the device electrical characteristics, V_{OVR} is 1.233V V. To limit $(R_2 + R_3) < 120$ k Ω , select $(R_2) = 100$ k Ω . Solving [Equation 7](#) gives $R_3 = 3.45$ k Ω .

Closest standard 1% resistor values are $R_2 = 100$ k Ω and $R_3 = 3.48$ k Ω .

10.3.2.5 MOSFET Q1 Selection

The V_{DS} rating of the MOSFET Q1 should be minimum 200 V for a output cutoff design where output can reach 0 V while the load dump transient is present and should be a minimum of 164.5 V when output is clamped to 37 V (± 1.5 V). The V_{GS} rating is based on HGATE-OUT maximum voltage of 15 V. A 20-V V_{GS} rated MOSFET is recommended.

Power dissipation on MOSFET Q1 on a design where output is clamped is critical and SOA characteristics of the MOSFET need to be considered with sufficient design margin for reliable operation.

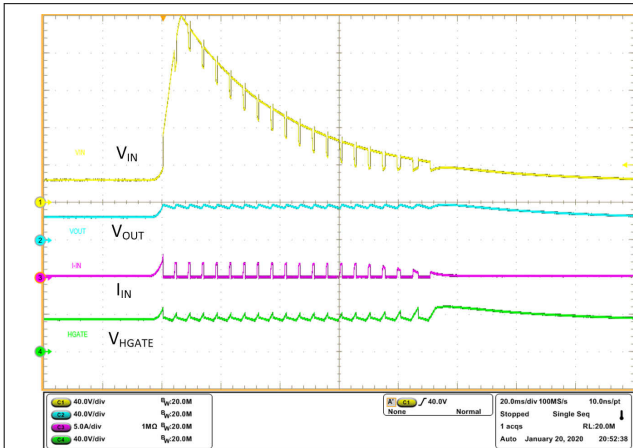
10.3.2.6 Input TVS Selection

Two TVS diodes D3 and D4 are required at the input. The breakdown voltage of TVS in the positive side should be higher than the maximum system voltage 200 V. On the negative side clamping, diode D4 is used to clamp ISO 7637-2 pulse 1 and its selection is similar to procedure in [TVS selection for 24-V Battery Systems](#). SMBJ150A for D3 and SMBJ33CA for D4 are recommended.

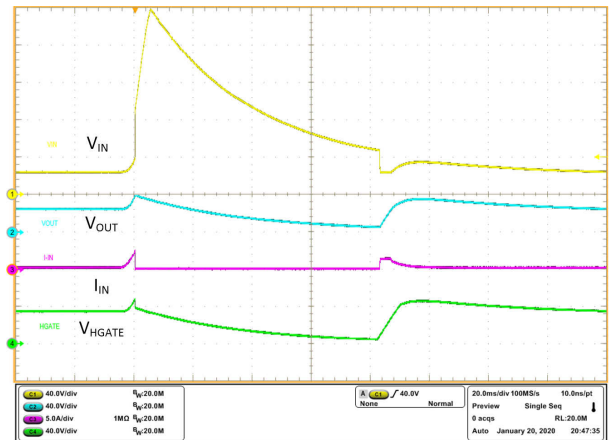
10.3.2.7 MOSFET Q2 Selection

Design requirements for selecting Q2 is similar to MOSFET Q1 selection in [表 10-1](#) and hence the procedure for selecting MOSFET Q2 is same as outlined in [MOSFET Selection: Blocking MOSFET Q1](#). MOSFET BUK7Y4R8-60E is selected based on the design requirements.

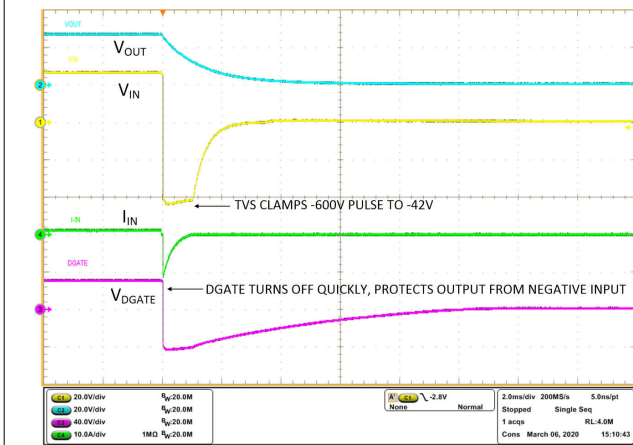
10.3.3 Application Curves



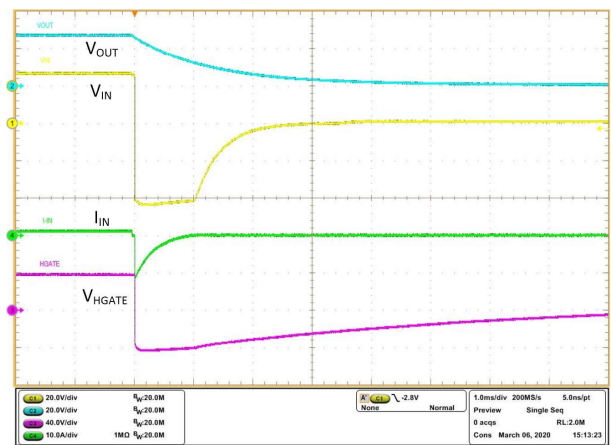
10-21. Unsuppressed Load Dump 200 V - Output Clamp



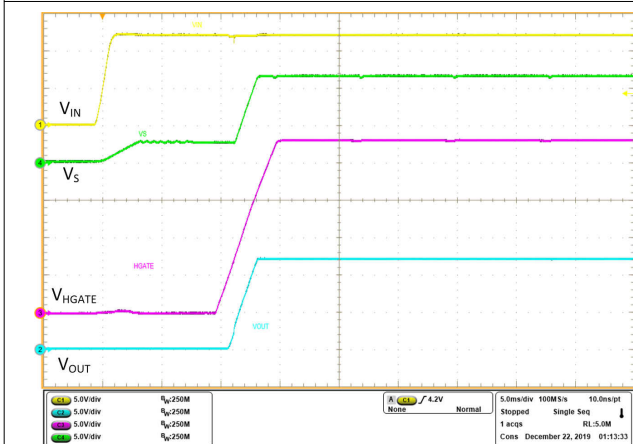
10-22. Unsuppressed Load Dump 200 V - Output Cut-off



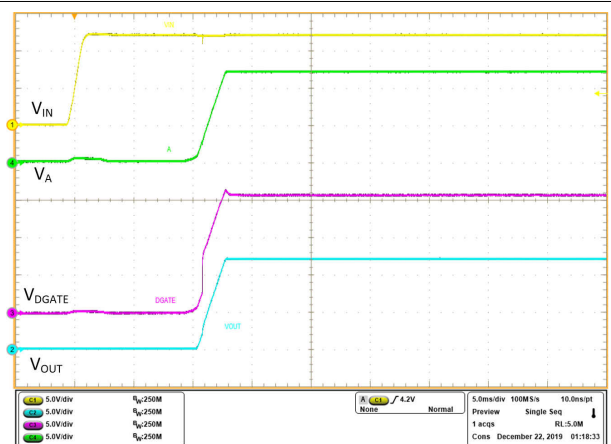
10-23. ISO 7637-2 Pulse 1 –600 V 50 Ω



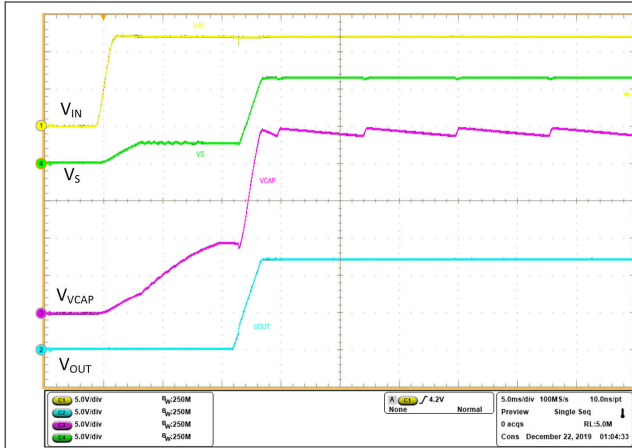
10-24. ISO 7637-2 Pulse 1 –600 V 50 Ω



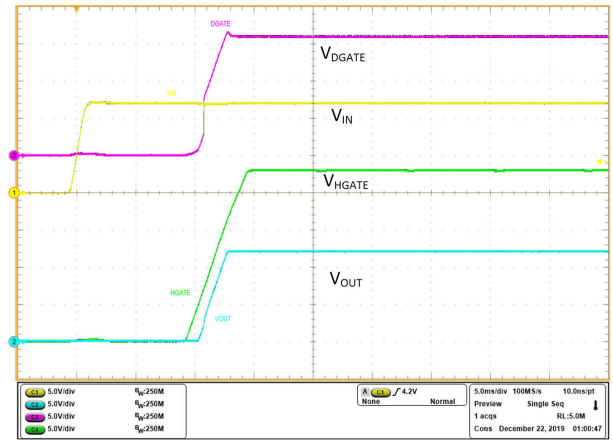
10-25. Power up 12 V - HGATE and Output



10-26. Power up 12 V - DGATE and A



10-27. Power up 12 V - Charge Pump VCAP



10-28. Power up 12 V - DGATE and HGATE

10.4 Do's and Don'ts

- Leave the exposed pad (RTN) of the IC floating. Do not connect the exposed pad to the GND plane. Connecting RTN to GND disables the reverse polarity protection feature.
- Connect a limiting resistor R_{PD} in series with the PD pin in the system application designs with input voltage above 48 V. This resistor value can be chosen in the range of 270 Ω to 330 Ω .

10.5 Power Supply Recommendations

10.5.1 Transient Protection

When the external MOSFETs turn OFF during the conditions such as overvoltage cut-off, reverse current blocking, EN/UVLO causing an interruption of the current flow, the input line inductance generates a positive voltage spike on the input and output inductance generates a negative voltage spike on the output. The peak amplitude of voltage spikes (transients) depends on the value of inductance in series to the input or output of the device. These transients can exceed the *Absolute Maximum Ratings* of the device if steps are not taken to address the issue.

Typical methods for addressing transients include:

- Minimizing lead length and inductance into and out of the device.
- Using large PCB GND plane.
- Use of a Schottky diode across the output and GND to absorb negative spikes.
- A low value ceramic capacitor ($C_{(IN)}$ to approximately 0.1 μF) to absorb the energy and dampen the transients.

The approximate value of input capacitance can be estimated with [Equation 8](#).

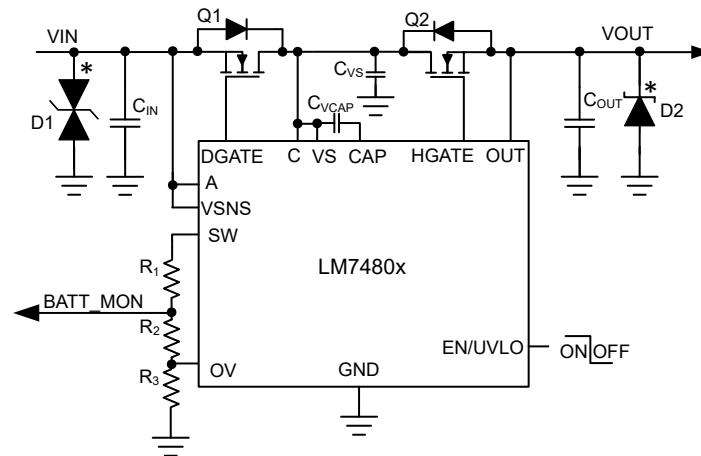
$$V_{\text{spike(Absolute)}} = V_{(IN)} + I_{(Load)} \times \sqrt{\frac{L_{(IN)}}{C_{(IN)}}} \quad (9)$$

where

- $V_{(IN)}$ is the nominal supply voltage
- $I_{(LOAD)}$ is the load current
- $L_{(IN)}$ equals the effective inductance seen looking into the source
- $C_{(IN)}$ is the capacitance present at the input

Some applications may require additional Transient Voltage Suppressor (TVS) to prevent transients from exceeding the *Absolute Maximum Ratings* of the device. These transients can occur during EMC testing such as automotive ISO7637 pulses.

The circuit implementation with optional protection components (a ceramic capacitor, TVS and schottky diode) is shown in [Figure 10-29](#)



* Optional components needed for suppression of transients

Figure 10-29. Circuit Implementation with Optional Protection Components for LM7480

10.5.2 TVS Selection for 12-V Battery Systems

In selecting the TVS, important specifications are breakdown voltage and clamping voltage. The breakdown voltage of the TVS+ should be higher than 24-V jump start voltage and 35-V suppressed load dump voltage and less than the maximum ratings of LM7480 (65 V). The breakdown voltage of TVS- should be beyond than maximum reverse battery voltage -16 V, so that the TVS- is not damaged due to long time exposure to reverse connected battery.

Clamping voltage is the voltage the TVS diode clamps in high current pulse situations and this voltage is much higher than the breakdown voltage. In the case of an ISO 7637-2 pulse 1, the input voltage goes up to -150 V with a generator impedance of 10Ω . This translates to 15 A flowing through the TVS - and the voltage across the TVS would be close to its clamping voltage.

The next criterion is that the absolute maximum rating of cathode to anode voltage of the LM7480 (85 V) and the maximum V_{DS} rating MOSFET are not exceeded. In the design example, 60-V rated MOSFET is chosen and maximum limit on the cathode to anode voltage is 60 V.

During ISO 7637-2 pulse 1, the anode of LM7480 is pulled down by the ISO pulse, clamped by TVS- and the MOSFET Q1 is turned off quickly to prevent reverse current from discharging the bulk output capacitors. When the MOSFET turns off, the cathode to anode voltage seen is equal to (TVS Clamping voltage + Output capacitor voltage). If the maximum voltage on output capacitor is 16 V (maximum battery voltage), then the clamping voltage of the TVS- should not exceed, $(60 \text{ V} - 16) \text{ V} = -44 \text{ V}$.

The SMBJ33CA TVS diode can be used for 12-V battery protection application. The breakdown voltage of 36.7 V meets the jump start, load dump requirements on the positive side and 16-V reverse battery connection on the negative side. During ISO 7637-2 pulse 1 test, the SMBJ33CA clamps at -44 V with 12 A of peak surge current as shown in and it meets the clamping voltage ≤ 44 V.

SMBJ series of TVS' are rated up to 600-W peak pulse power levels and are sufficient for ISO 7637-2 pulses.

10.5.3 TVS Selection for 24-V Battery Systems

For 24-V battery protection application, the TVS and MOSFET in [Figure 10-1](#) needs to be changed to suit 24-V battery requirements.

The breakdown voltage of the TVS+ should be higher than 48-V jump start voltage, less than the absolute maximum ratings of anode and enable pin of LM7480 (70 V) and should withstand 65-V suppressed load dump.

The breakdown voltage of TVS- should be lower than maximum reverse battery voltage -32 V , so that the TVS- is not damaged due to long time exposure to reverse connected battery.

During ISO 7637-2 pulse 1, the input voltage goes up to -600 V with a generator impedance of $50\ \Omega$. This translates to 12-A flowing through the TVS-. The clamping voltage of the TVS- cannot be same as that of 12-V battery protection circuit. Because during the ISO 7637-2 pulse, the Anode to Cathode voltage seen is equal to $(- \text{TVS Clamping voltage} + \text{Output capacitor voltage})$. For 24-V battery application, the maximum battery voltage is 32 V , then the clamping voltage of the TVS- should not exceed, $85\text{ V} - 32\text{ V} = 53\text{ V}$.

Single bi-directional TVS cannot be used for 24-V battery protection because breakdown voltage for TVS+ $\geq 65\text{V}$, maximum clamping voltage is $\leq 53\text{ V}$ and the clamping voltage cannot be less than the breakdown voltage. Two un-directional TVS connected back-back needs to be used at the input. For positive side TVS+, SMBJ58A with the breakdown voltage of 64.4 V (minimum), 67.8 (typical) is recommended. For the negative side TVS-, SMBJ28A with breakdown voltage close to 32 V (to withstand maximum reverse battery voltage -32 V) and maximum clamping voltage of 42.1 V is recommended.

For 24-V battery protection, a 75-V rated MOSFET is recommended to be used along with SMBJ28A and SMBJ58A connected back-back at the input.

10.6 Layout

10.6.1 Layout Guidelines

- For the ideal diode stage, connect A, GATE and C pins of LM74720-Q1 close to the MOSFET's SOURCE, GATE and DRAIN pins.
- The high current path of for this solution is through the MOSFET; therefore, it is important to use thick and short traces for source and drain of the MOSFET to minimize resistive losses.
- The GATE pin of the LM74720-Q1 must be connected to the MOSFET GATE with short trace.
- Boost converter switching currents flow into LX, CAP, GND pins and C3 (across DRAIN of the FET to GND). The loops formed by capacitor across CAP pin and DRAIN of the FET and C3 to GND must be minimized by placing these capacitors as close as possible. Keep the GND side of the C3 capacitor close to GND pin of LM74720-Q1.
- Place transient suppression components like input TVS and output Schottky close to LM74720-Q1.

10.6.2 Layout Example

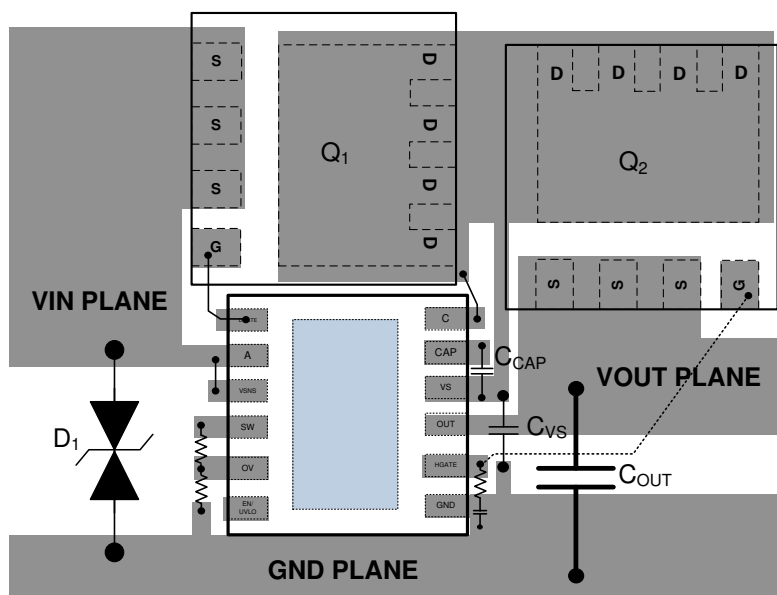
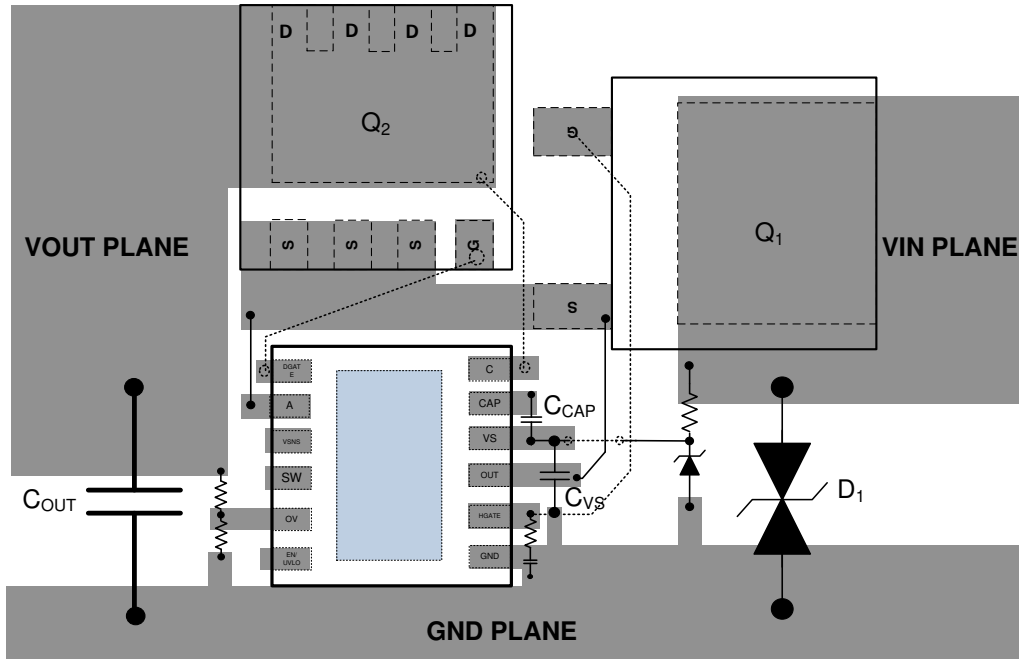


FIG 10-30. PCB Layout Example for Common Drain Configuration



10-31. PCB Layout Example for Common Source Configuration

11 Device and Documentation Support

11.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[ti.com](https://www.ti.com) のデバイス製品フォルダを開いてください。「更新の通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

11.2 サポート・リソース

TI E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

リンクされているコンテンツは、該当する貢献者により、現状のまま提供されるものです。これらは TI の仕様を構成するものではなく、必ずしも TI の見解を反映したものではありません。TI の[使用条件](#)を参照してください。

11.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

11.4 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

11.5 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LM74800MDRRR	ACTIVE	WSON	DRR	12	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	ET7480	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF LM7480 :

- Automotive : [LM7480-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

GENERIC PACKAGE VIEW

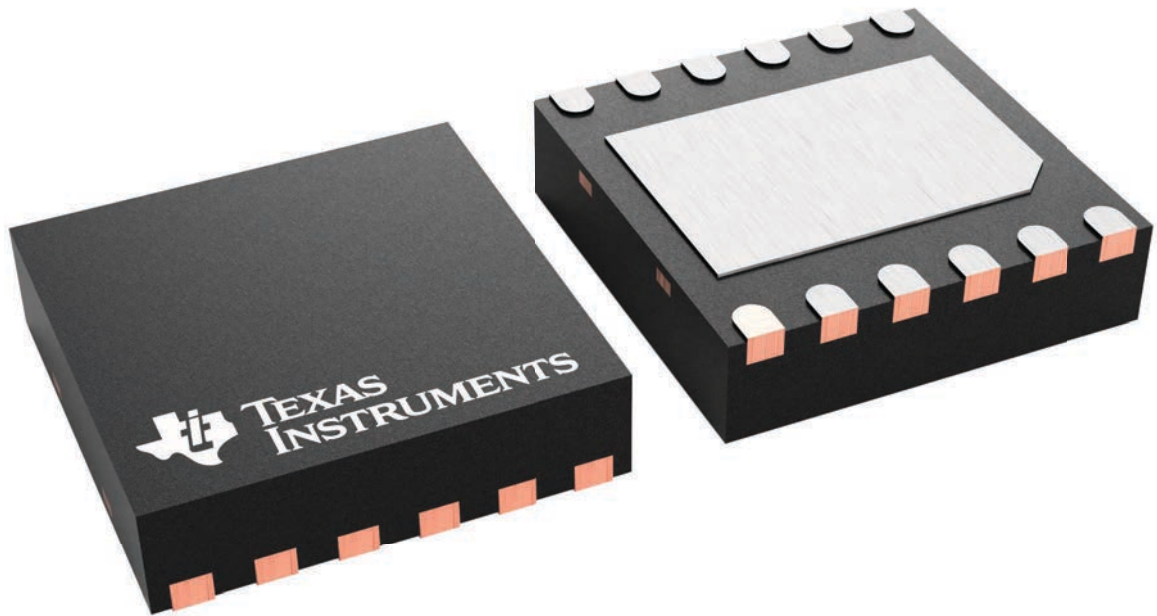
DRR 12

WSON - 0.8 mm max height

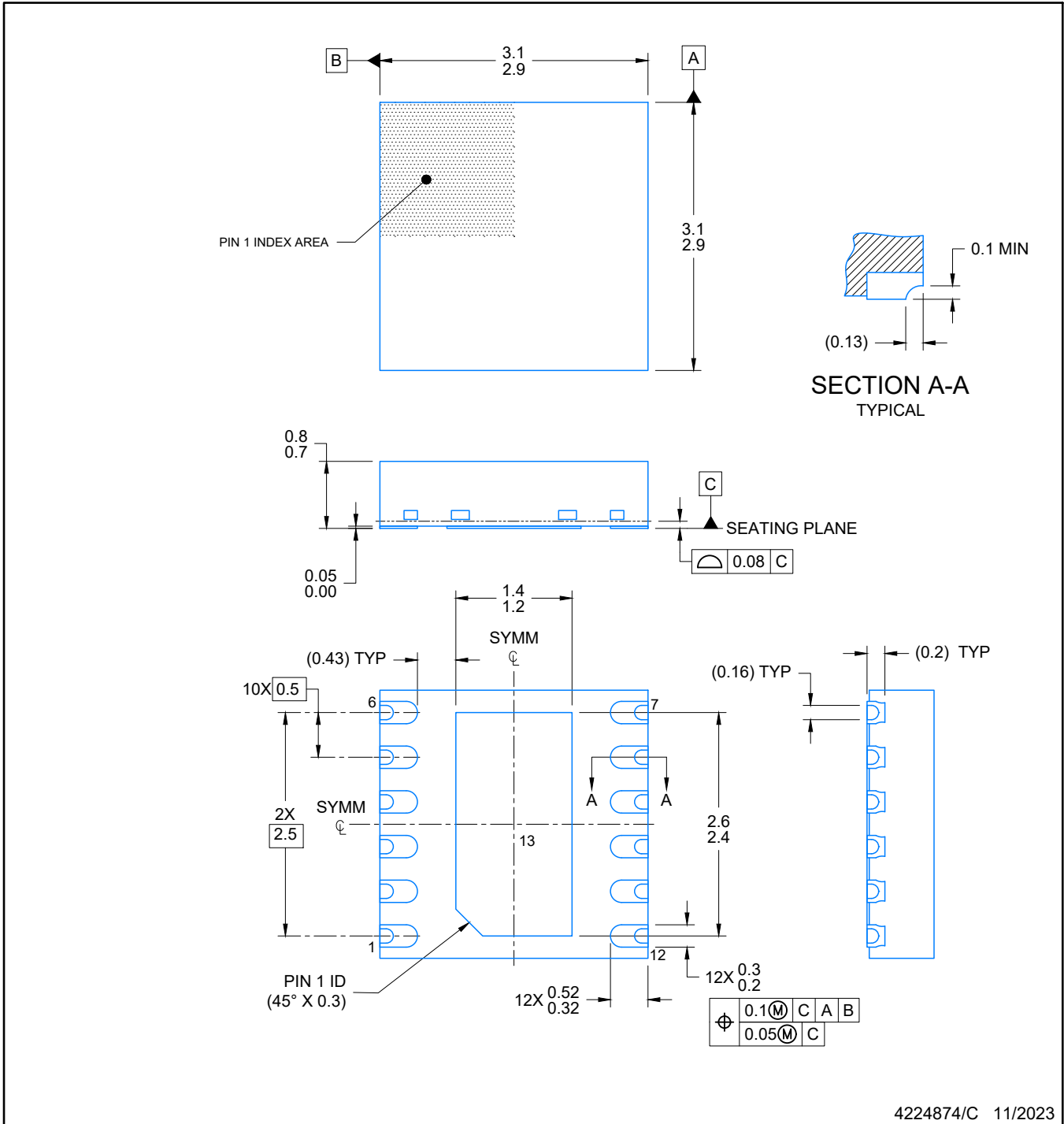
3 x 3, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4223490/B



NOTES:

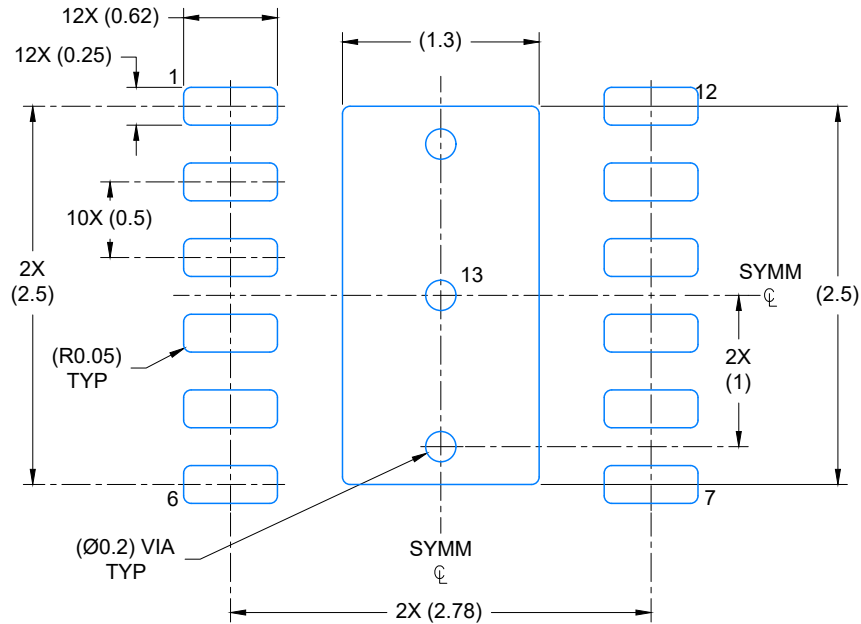
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

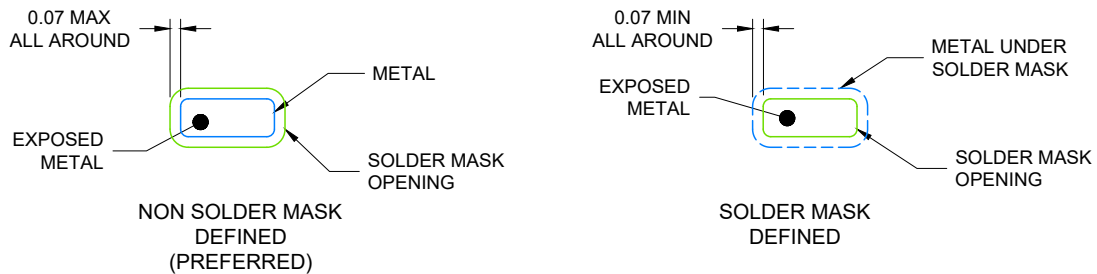
WSON - 0.8 mm max height

DRR0012E

PLASTIC QUAD FLAT PACK- NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



SOLDER MASK DETAILS

4224874/C 11/2023

NOTES: (continued)

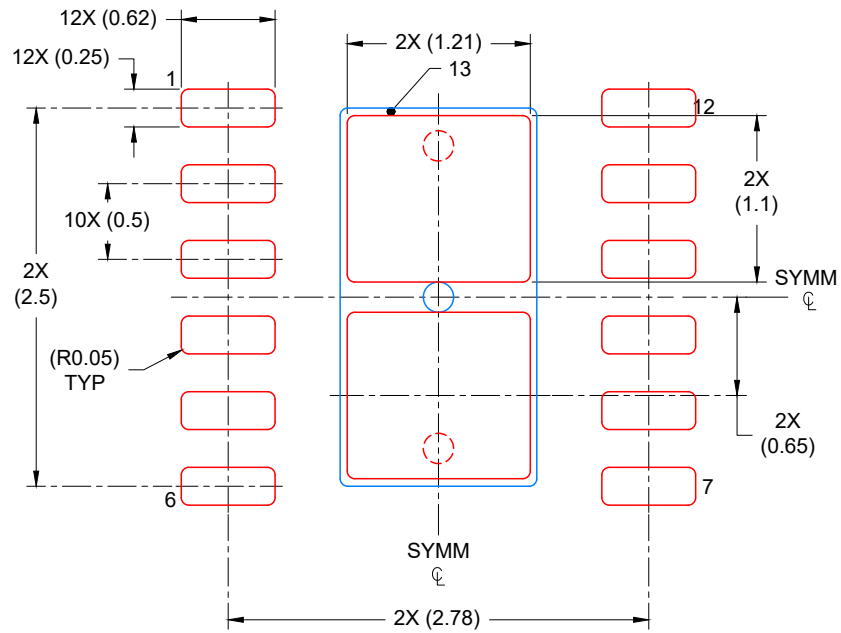
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

DRR0012E

WSON - 0.8 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
82% PRINTED COVERAGE BY AREA
SCALE: 20X

4224874/C 11/2023

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

重要なお知らせと免責事項

TI は、技術データと信頼性データ（データシートを含みます）、設計リソース（リファレンス・デザインを含みます）、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、TI 製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した TI 製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとし、

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている TI 製品を使用するアプリケーションの開発の目的でのみ、TI はその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。TI や第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、TI およびその代理人を完全に補償するものとし、TI は一切の責任を拒否します。

TI の製品は、[TI の販売条件](#)、または [ti.com](#) やかかる TI 製品の関連資料などのいずれかを通じて提供する適用可能な条項の下で提供されています。TI がこれらのリソースを提供することは、適用される TI の保証または他の保証の放棄の拡大や変更を意味するものではありません。

お客様がいかなる追加条項または代替条項を提案した場合でも、TI はそれらに異議を唱え、拒否します。

郵送先住所：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2024, Texas Instruments Incorporated